Yasuhiko Arakawa

List of Publications by Year
in descending order

663 papers	26,765 citations	9756 73 h-index	9839 141 g-index
671 all docs	671 docs citations	671 times ranked	12842 citing authors

#	Article	IF	Citations
1	Multidimensional quantum well laser and temperature dependence of its threshold current. Applied Physics Letters, 1982, 40, 939-941.	1.5	3,197
2	Observation of the coupled exciton-photon mode splitting in a semiconductor quantum microcavity. Physical Review Letters, 1992, 69, 3314-3317.	2.9	2,140
3	Quantum well lasers--Gain, spectra, dynamics. IEEE Journal of Quantum Electronics, 1986, 22, 1887-1899.	1.0	524
4	A gallium nitride single-photon source operating at 200â€‰K. Nature Materials, 2006, 5, 887-892.	13.3	388
5	Efficient Carrier Relaxation Mechanism in InGaAs/GaAs Self-Assembled Quantum Dots Based on the Existence of Continuum States. Physical Review Letters, 1999, 82, 4114-4117.	2.9	341
6	Room-Temperature Triggered Single Photon Emission from a III-Nitride Site-Controlled Nanowire Quantum Dot. Nano Letters, 2014, 14, 982-986.	4.5	337
7	Laser oscillation in a strongly coupled single-quantum-dotâ€“nanocavity system. Nature Physics, 2010, 6, 279-283.	6.5	300
8	Rapid carrier relaxation in self-assembledInxGa1âˆ'xAs/GaAs quantum dots. Physical Review B, 1996, 54, 11532-11538.	1.1	289
9	Fabrication of InAs/GaAs quantum dot solar cells with enhanced photocurrent and without degradation of open circuit voltage. Applied Physics Letters, 2010, 96, .	1.5	281
10	Photonic crystal nanocavity based on a topological corner state. Optica, 2019, 6, 786.	4.8	274
11	Over 1.5 Î¼m light emission from InAs quantum dots embedded in InGaAs strain-reducing layer grown by metalorganic chemical vapor deposition. Applied Physics Letters, 2001, 78, 3469-3471.	1.5	259
12	Highly uniform InGaAs/GaAs quantum dots (âˆ¼15 nm) by metalorganic chemical vapor deposition. Applied Physics Letters, 1994, 65, 1421-1423.	1.5	242
13	Theory of gain, modulation response, and spectral linewidth in AlGaAs quantum well lasers. IEEE Journal of Quantum Electronics, 1985, 21, 1666-1674.	1.0	241
14	Quantum noise and dynamics in quantum well and quantum wire lasers. Applied Physics Letters, 1984, 45, 950-952.	1.5	237
15	Room Temperature Lasing at Blue Wavelengths in Gallium Nitride Microcavities. Science, 1999, 285, 1905-1906.	6.0	237
16	Recent progress in self-assembled quantum-dot optical devices for optical telecommunication: temperature-insensitive 10â€‰Gbâ€‰sâˆ'1directly modulated lasers and 40â€‰Gbâ€‰sâˆ'1signal-regenerative amplifiers. Journal Physics D: Applied Physics, 2005, 38, 2126-2134.	1.3	224
17	Nanometer-scale InGaN self-assembled quantum dots grown by metalorganic chemical vapor deposition. Applied Physics Letters, 1999, 74, 383-385.	1.5	197
18	Time-resolved vacuum Rabi oscillations in a semiconductor quantum microcavity. Physical Review B, 1994, 50, 14663-14666.	1.1	195

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19	Room temperature continuous-wave lasing in photonic crystal nanocavity. Optics Express, 2006, 14, 6308.	1.7	186
20	Progress in quantum-dot single photon sources for quantum information technologies: A broad spectrum overview. Applied Physics Reviews, 2020, 7, .	5.5	184
21	Phonon bottleneck in quantum dots:â€ƒRole of lifetime of the confined optical phonons. Physical Review B, 1999, 59, 5069-5073.	1.1	180
22	An ultrawide-band semiconductor optical amplifier having an extremely high penalty-free output power of 23 dBm achieved with quantum dots. IEEE Photonics Technology Letters, 2005, 17, 1614-1616.	1.3	178
23	Pentacene-based organic field-effect transistors. Journal of Physics Condensed Matter, 2008, 20, 184011.	0.7	176
24	Fabrication of GaAs quantum wires on epitaxially grown V grooves by metalâ€organic chemicalâ€vapor deposition. Journal of Applied Physics, 1992, 71, 533-535.	1.1	173
25	Lasing oscillation in a three-dimensional photonic crystal nanocavity with a complete bandgap. Nature Photonics, 2011, 5, 91-94.	15.6	173
26	Active topological photonics. Nanophotonics, 2020, 9, 547-567.	2.9	170
27	Coupling of quantum-dot light emission with a three-dimensional photonic-crystal nanocavity. Nature Photonics, 2008, 2, 688-692.	15.6	166
28	In situ fabrication of selfâ€aligned InGaAs quantum dots on GaAs multiatomic steps by metalorganic chemical vapor deposition. Applied Physics Letters, 1995, 66, 3663-3665.	1.5	164
29	Temperature-Insensitive Eye-Opening under 10-Gb/s Modulation of 1.3-Âµm P-Doped Quantum-Dot Lasers without Current Adjustments. Japanese Journal of Applied Physics, 2004, 43, L1124-L1126.	0.8	163
30	Room-temperature lasing in a single nanowire with quantum dots. Nature Photonics, 2015, 9, 501-505.	15.6	159
31	Topological photonic crystal nanocavity laser. Communications Physics, 2018, 1, .	2.0	154
32	A Hybrid Integrated Light Source on a Silicon Platform Using a Trident Spot-Size Converter. Journal of Lightwave Technology, 2014, 32, 1329-1336.	2.7	152
33	Quantum key distribution over 120â€‰km using ultrahigh purity single-photon source and superconducting single-photon detectors. Scientific Reports, 2015, 5, 14383.	1.6	152
34	Photoluminescence spectra and anisotropic energy shift of GaAs quantum wires in high magnetic fields. Physical Review Letters, 1992, 69, 2963-2966.	2.9	147
35	Si Photonic Wire Waveguide Devices. IEEE Journal of Selected Topics in Quantum Electronics, 2006, 12, 1371-1379.	1.9	141
36	Narrow photoluminescence peaks from localized states in InGaN quantum dot structures. Applied Physics Letters, 2000, 76, 2361-2363.	1.5	131

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37	Compact 1 Ã— N thermo-optic switches based on silicon photonic wire waveguides. Optics Express, 2005, 13, 10109.	1.7	131
38	High-efficiency InAs/GaAs quantum dot solar cells by metalorganic chemical vapor deposition. Applied Physics Letters, 2012, 100, .	1.5	131
39	Structural and optical properties of type II GaSb/GaAs self-assembled quantum dots grown by molecular beam epitaxy. Journal of Applied Physics, 1999, 85, 8349-8352.	1.1	128
40	Optical directional coupler based on Si-wire waveguides. IEEE Photonics Technology Letters, 2005, 17, 585-587.	1.3	125
41	Spontaneous Two-Photon Emission from a Single Quantum Dot. Physical Review Letters, 2011, 107, 233602.	2.9	124
42	High-density and size-controlled GaN self-assembled quantum dots grown by metalorganic chemical vapor deposition. Applied Physics Letters, 2002, 80, 3937-3939.	1.5	122
43	Single-Photon Generation in the 1.55-Âµm Optical-Fiber Band from an InAs/InP Quantum Dot. Japanese Journal of Applied Physics, 2005, 44, L620-L622.	0.8	120
44	Progress in GaN-based quantum dots for optoelectronics applications. IEEE Journal of Selected Topics in Quantum Electronics, 2002, 8, 823-832.	1.9	116
45	Ectopically expressed PDX-1 in liver initiates endocrine and exocrine pancreas differentiation but causes dysmorphogenesis. Biochemical and Biophysical Research Communications, 2003, 310, 1017-1025.	1.0	115
46	Organic light-emitting diodes driven by pentacene-based thin-film transistors. Applied Physics Letters, 2003, 83, 3410-3412.	1.5	111
47	Photonic crystal nanocavity laser with a single quantum dot gain. Optics Express, 2009, 17, 15975.	1.7	110
48	Highly reflective GaN/Al0.34Ga0.66N quarter-wave reflectors grown by metal organic chemical vapor deposition. Applied Physics Letters, 1998, 73, 3653-3655.	1.5	109
49	First Demonstration of Athermal Silicon Optical Interposers With Quantum Dot Lasers Operating up to 125 Â°C. Journal of Lightwave Technology, 2015, 33, 1223-1229.	2.7	106
50	Atomic structure and phase stability ofInxGa1â^'xNrandom alloys calculated using a valence-force-field method. Physical Review B, 1999, 60, 1701-1706.	1.1	104
51	Selective-area growth of thin GaN nanowires by MOCVD. Journal of Crystal Growth, 2012, 357, 58-61.	0.7	103
52	Selective growth of InGaN quantum dot structures and their microphotoluminescence at room temperature. Applied Physics Letters, 2000, 76, 3212-3214.	1.5	102
53	All MBE grown InAs/GaAs quantum dot lasers on on-axis Si (001). Optics Express, 2018, 26, 11568.	1.7	101
54	Detailed balance limit of the efficiency of multilevel intermediate band solar cells. Applied Physics Letters, 2011, 98, .	1.5	100

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55	Electronic structure of piezoelectric In0.2Ga0.8N quantum dots in GaN calculated using a tight-binding method. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 15, 169-181.	1.3	97
56	Fabrication of GaAs quantum wires (âˆ¼10 nm) by metalorganic chemical vapor selective deposition growth. Applied Physics Letters, 1993, 63, 355-357.	1.5	94
57	An optical horn structure for single-photon source using quantum dots at telecommunication wavelength. Journal of Applied Physics, 2007, 101, 081720.	1.1	93
58	Exciton and biexciton luminescence from single hexagonal GaNâˆ•AlN self-assembled quantum dots. Applied Physics Letters, 2004, 85, 64-66.	1.5	92
59	Low-Threshold near-Infrared GaAsâ€"AlGaAs Coreâ€"Shell Nanowire Plasmon Laser. ACS Photonics, 2015, 2, 165-171.	3.2	92
60	Slow light waveguides in topological valley photonic crystals. Optics Letters, 2020, 45, 2648.	1.7	91
61	First demonstration of high density optical interconnects integrated with lasers, optical modulators, and photodetectors on single silicon substrate. Optics Express, 2011, 19, B159.	1.7	90
62	Photon lifetime dependence of modulation efficiency and K factor in 1.3Î¼m self-assembled InAsâˆ•GaAs quantum-dot lasers: Impact of capture time and maximum modal gain on modulation bandwidth. Applied Physics Letters, 2004, 85, 4145-4147.	1.5	88
63	Electrically pumped 13 Î¼m room-temperature InAs/GaAs quantum dot lasers on Si substrates by metal-mediated wafer bonding and layer transfer. Optics Express, 2010, 18, 10604.	1.7	84
64	Strong coupling between a photonic crystal nanobeam cavity and a single quantum dot. Applied Physics Letters, 2011, 98, .	1.5	84
65	Single-photon emission at 1.5â€‰<i>Î¼</i>m from an InAs/InP quantum dot with highly suppressed multi-photon emission probabilities. Applied Physics Letters, 2016, 109, .	1.5	83
66	Room-temperature lasing oscillation in an InGaN self-assembled quantum dot laser. Applied Physics Letters, 1999, 75, 2605-2607.	1.5	82
67	1.5-Î¼m-wavelength light guiding in waveguides in square-lattice-of-rod photonic crystal slab. Applied Physics Letters, 2004, 84, 4298-4300.	1.5	81
68	Second quantized state lasing of a current pumped single quantum well laser. Applied Physics Letters, 1986, 49, 1689-1691.	1.5	80
69	Transfer-printed single-photon sources coupled to wire waveguides. Optica, 2018, 5, 691.	4.8	76
70	Size-dependent radiative decay time of excitons in GaN/AlN self-assembled quantum dots. Applied Physics Letters, 2003, 83, 984-986.	1.5	75
71	Artificial control of optical gain polarization by stacking quantum dot layers. Applied Physics Letters, 2006, 88, 211106.	1.5	75
72	Ultraclean Single Photon Emission from a GaN Quantum Dot. Nano Letters, 2017, 17, 2902-2907.	4.5	75

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73	Doseâ€dependent mixing of AlAsâ€GaAs superlattices by Si ion implantation. Applied Physics Letters, 1986, 49, 701-703.	1.5	73
74	Lasing Emission from an In0.1Ga0.9N Vertical Cavity Surface Emitting Laser. Japanese Journal of Applied Physics, 1998, 37, L1424-L1426.	0.8	73
75	Single Photons from a Hot Solid-State Emitter at 350 K. ACS Photonics, 2016, 3, 543-546.	3.2	73
76	Influence of strain relaxation of the AlxGa1â^'xN barrier on transport properties of the two-dimensional electron gas in modulation-doped AlxGa1â^'xN/GaN heterostructures. Applied Physics Letters, 2000, 76, 2746-2748.	1.5	72
77	Non-classical Photon Emission from a Single InAs/InP Quantum Dot in the 1.3-Âµm Optical-Fiber Band. Japanese Journal of Applied Physics, 2004, 43, L993-L995.	0.8	71
78	Photon correlation studies of single GaN quantum dots. Applied Physics Letters, 2005, 87, 051916.	1.5	71
79	Kondo effect in a semiconductor quantum dot coupled to ferromagnetic electrodes. Applied Physics Letters, 2007, 91, .	1.5	70
80	Fabrication of GaAs arrowheadâ€shaped quantum wires by metalorganic chemical vapor deposition selective growth. Applied Physics Letters, 1993, 62, 49-51.	1.5	68
81	Near-field magneto-optical spectroscopy of single self-assembled InAs quantum dots. Applied Physics Letters, 1998, 73, 517-519.	1.5	68
82	X-chromosomal localization of mammalian Y-linked genes in two XO species of the Ryukyu spiny rat. Cytogenetic and Genome Research, 2002, 99, 303-309.	0.6	66
83	Nonlinear-Optic Silicon-Nanowire Waveguides. Japanese Journal of Applied Physics, 2005, 44, 6541-6545.	0.8	66
84	Systematic Study of the Effects of Modulation p-Doping on 1.3-$mu{hbox {m}}$ Quantum-Dot Lasers. IEEE Journal of Quantum Electronics, 2007, 43, 1129-1139.	1.0	65
85	Low-voltage-operating complementary inverters with C60 and pentacene transistors on glass substrates. Applied Physics Letters, 2007, 91, 053505.	1.5	65
86	Molecular analysis of Clostridium difficile at a university teaching hospital in Japan: a shift in the predominant type over a five-year period. European Journal of Clinical Microbiology and Infectious Diseases, 2007, 26, 695-703.	1.3	65
87	Recombination lifetime of carriers in GaAsâ€GaAlAs quantum wells near room temperature. Applied Physics Letters, 1985, 46, 519-521.	1.5	64
88	Optical linewidths in an individual quantum dot. Physical Review B, 1999, 60, 1915-1920.	1.1	64
89	Organic/inorganic hybrid complementary circuits based on pentacene and amorphous indium gallium zinc oxide transistors. Applied Physics Letters, 2008, 93, .	1.5	64
90	A Nanowire-Based Plasmonic Quantum Dot Laser. Nano Letters, 2016, 16, 2845-2850.	4.5	64

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91	GaAs quantum dots with lateral dimension of 25 nm fabricated by selective metalorganic chemical vapor deposition growth. Applied Physics Letters, 1994, 64, 2495-2497.	1.5	63
92	Anharmonic decay of confined optical phonons in quantum dots. Physical Review B, 1998, 57, 12285-12290.	1.1	63
93	Threshold voltage control of bottom-contact n-channel organic thin-film transistors using modified drain/source electrodes. Applied Physics Letters, 2009, 94, .	1.5	61
94	Narrow photoluminescence linewidth (<17â€‚meV) from highly uniform self-assembled InAs/GaAs quantum dots grown by low-pressure metalorganic chemical vapor deposition. Applied Physics Letters, 2004, 84, 2817-2819.	1.5	60
95	Observation of enhanced photoluminescence from silicon photonic crystal nanocavity at room temperature. Applied Physics Letters, 2007, 91, .	1.5	60
96	Enhanced and inhibited spontaneous emission in GaAs/AlGaAs vertical microcavity lasers with two kinds of quantum wells. Applied Physics Letters, 1991, 58, 2339-2341.	1.5	59
97	Exciton fine-structure splitting in GaN/AlN quantum dots. Physical Review B, 2010, 81, .	1.1	59
98	Occupation of the double subbands by the two-dimensional electron gas in the triangular quantum well atAlxGa1â^’xN/GaNheterostructures. Physical Review B, 2000, 62, R7739-R7742.	1.1	58
99	Shell structures in self-assembled InAs quantum dots probed by lateral electron tunneling structures. Applied Physics Letters, 2005, 87, 203109.	1.5	58
100	Hybrid p-n junction light-emitting diodes based on sputtered ZnO and organic semiconductors. Applied Physics Letters, 2009, 95, .	1.5	58
101	Transmission Experiment of Quantum Keys over 50 km Using High-Performance Quantum-Dot Single-Photon Source at 1.5 Âµm Wavelength. Applied Physics Express, 2010, 3, 092802.	1.1	58
102	Fabrication of quantum wires and dots by MOCVD selective growth. Solid-State Electronics, 1994, 37, 523-528.	0.8	57
103	Near-field coherent excitation spectroscopy of InGaAs/GaAs self-assembled quantum dots. Applied Physics Letters, 2000, 76, 3887-3889.	1.5	56
104	Polarized photoluminescence spectroscopy of single self-assembled InAs quantum dots. Physical Review B, 1998, 58, R10147-R10150.	1.1	55
105	Nearly diffraction-limited focusing of a fiber axicon microlens. Review of Scientific Instruments, 2003, 74, 4969-4971.	0.6	55
106	AlN air-bridge photonic crystal nanocavities demonstrating high quality factor. Applied Physics Letters, 2007, 91, 051106.	1.5	55
107	Room temperature continuous wave operation of InAs/GaAs quantum dot photonic crystal nanocavity laser on silicon substrate. Optics Express, 2009, 17, 7036.	1.7	55
108	Recent progress in topological waveguides and nanocavities in a semiconductor photonic crystal platform [Invited]. Optical Materials Express, 2021, 11, 319.	1.6	55

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109	Control of optical polarization anisotropy in edge emitting luminescence of InAs/GaAs self-assembled quantum dots. Applied Physics Letters, 2004, 84, 1820-1822.	1.5	54
110	Nonlinear gain effects due to carrier heating and spectral holeburning in strained-quantum-well lasers. IEEE Photonics Technology Letters, 1992, 4, 682-685.	1.3	53
111	Demonstration of 125-Gbps optical interconnects integrated with lasers, optical splitters, optical modulators and photodetectors on a single silicon substrate. Optics Express, 2012, 20, B256.	1.7	53
112	Enhancement of carbon nanotube photoluminescence by photonic crystal nanocavities. Applied Physics Letters, 2012, 101, 141124.	1.5	53
113	Spectral diffusion and its influence on the emission linewidths of site-controlled GaN nanowire quantum dots. Physical Review B, 2015, 92, .	1.1	53
114	Thresholdless quantum dot nanolaser. Optics Express, 2017, 25, 19981.	1.7	53
115	MOCVD-grown InGaN-channel HEMT structures with electron mobility of over. Journal of Crystal Growth, 2004, 272, 278-284.	0.7	52
116	The Electronic Properties of DNA Bases. Small, 2007, 3, 1539-1543.	5.2	51
117	Current-gain cutoff frequencies above 10 MHz for organic thin-film transistors with high mobility and low parasitic capacitance. Applied Physics Letters, 2009, 95, .	1.5	51
118	Ultrafast energy relaxation in quantum dots through defect states: A lattice-relaxation approach. Physical Review B, 1997, 56, 10423-10427.	1.1	50
119	High density InAsâˆ•GaAs quantum dots with enhanced photoluminescence intensity using antimony surfactant-mediated metal organic chemical vapor deposition. Applied Physics Letters, 2006, 89, 183124.	1.5	50
120	Growth process and mechanism of nanometer-scale GaAs dot-structures using MOCVD selective growth. Journal of Crystal Growth, 1993, 126, 707-717.	0.7	49
121	Spatially and spectrally resolved imaging of GaAs quantumâ€dot structures using nearâ€field optical technique. Applied Physics Letters, 1996, 69, 827-829.	1.5	49
122	Time-resolved dynamics in single InGaN quantum dots. Applied Physics Letters, 2003, 83, 2674-2676.	1.5	49
123	ActiveQswitching in a GaAs/AlGaAs multiquantum well laser with an intracavity monolithic loss modulator. Applied Physics Letters, 1986, 48, 561-563.	1.5	48
124	Quantum-dot single-photon source on a CMOS silicon photonic chip integrated using transfer printing. APL Photonics, 2019, 4, 036105.	3.0	48
125	Picosecond pulse generation (<1.8 ps) in a quantum well laser by a gain switching method. Applied Physics Letters, 1987, 51, 1295-1297.	1.5	47
126	InAsâˆ•GaAs self-assembled quantum-dot lasers grown by metalorganic chemical vapor depositionâ€"Effects of postgrowth annealing on stacked InAs quantum dots. Applied Physics Letters, 2004, 85, 1024-1026.	1.5	47

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127	Unconventional quantum-confined Stark effect in a singleGaNquantum dot. Physical Review B, 2006, 73, .	1.1	47
128	Site-controlled formation of InAs/GaAs quantum-dot-in-nanowires for single photon emitters. Applied Physics Letters, 2012, 100, .	1.5	47
129	Tight-binding analysis of energy-band structures in quantum wires. Physical Review B, 1991, 43, 4732-4738.	1.1	46
130	Femtosecond dynamics of semiconductor-microcavity polaritons in the nonlinear regime. Solid State Communications, 1996, 97, 941-946.	0.9	46
131	Bottom-contact fullerene C60 thin-film transistors with high field-effect mobilities. Applied Physics Letters, 2008, 93, 033313.	1.5	46
132	Atomistic Insights for InAs Quantum Dot Formation on GaAs(001) using STM within a MBE Growth Chamber. Small, 2006, 2, 386-389.	5.2	45
133	Exciton acoustic-phonon coupling in single GaN/AlN quantum dots. Physical Review B, 2012, 85, .	1.1	45
134	Density Control of GaSb/GaAs Self-assembled Quantum Dots (âˆ¼25nm) Grown by Molecular Beam Epitaxy. Japanese Journal of Applied Physics, 1998, 37, L203-L205.	0.8	44
135	Area-controlled growth of InAs quantum dots and improvement of density and size distribution. Applied Physics Letters, 2000, 77, 3382-3384.	1.5	44
136	Room temperature continuous wave lasing in InAs quantum-dot microdisks with air cladding. Optics Express, 2005, 13, 1615.	1.7	44
137	Manifestation of unconventional biexciton states in quantum dots. Nature Communications, 2014, 5, 5721.	5.8	44
138	Single-photon emission from cubic GaN quantum dots. Applied Physics Letters, 2014, 104, .	1.5	44
139	Emission of Linearly Polarized Single Photons from Quantum Dots Contained in Nonpolar, Semipolar, and Polar Sections of Pencil-Like InGaN/GaN Nanowires. ACS Photonics, 2017, 4, 657-664.	3.2	44
140	Fabrication of InAs quantum dots on InP(100) by metalorganic vapor-phase epitaxy for 1.55 Î¼m optical device applications. Applied Physics Letters, 2004, 85, 4331.	1.5	43
141	High-Q design of semiconductor-based ultrasmall photonic crystal nanocavity. Optics Express, 2010, 18, 8144.	1.7	43
142	High-temperature continuous-wave operation of directly grown InAs/GaAs quantum dot lasers on on-axis Si (001). Optics Express, 2019, 27, 2681.	1.7	43
143	Enhanced modulation bandwidth of GaAlAs double heterostructure lasers in high magnetic fields: Dynamic response with quantum wire effects. Applied Physics Letters, 1985, 47, 1142-1144.	1.5	42
144	Low threshold current operation of self-assembled InAsâˆ•GaAs quantum dot lasers by metal organic chemicalvapour deposition. Electronics Letters, 2003, 39, 1130.	0.5	42

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145	Formation and optical properties of stacked GaN self-assembled quantum dots grown by metalorganic chemical vapor deposition. Applied Physics Letters, 2004, 85, 1262-1264.	1.5	42
146	Time-of-Flight Measurement of Lateral Carrier Mobility in Organic Thin Films. Japanese Journal of Applied Physics, 2004, 43, 2326-2329.	0.8	41
147	Vacuum Rabi splitting with a single quantum dot embedded in a H1 photonic crystal nanocavity. Applied Physics Letters, 2009, 94, .	1.5	41
148	Light emission from zeroâ€dimensional excitonsâ€"Photoluminescence from quantum wells in strong magnetic fields. Applied Physics Letters, 1985, 46, 83-85.	1.5	40
149	Area Density Control of Quantum-Size InGaAs/Ga(Al)As Dots by Metalorganic Chemical Vapor Deposition. Japanese Journal of Applied Physics, 1994, 33, L1634-L1637.	0.8	40
150	High-density and wide-bandwidth optical interconnects with silicon optical interposers [Invited]. Photonics Research, 2014, 2, A1.	3.4	40
151	Experimental demonstration of topological slow light waveguides in valley photonic crystals. Optics Express, 2021, 29, 13441.	1.7	40
152	Oneâ€dimensional exciton diffusion in GaAs quantum wires. Applied Physics Letters, 1995, 67, 1535-1537.	1.5	39
153	Ground state lasing at 1.34Î¼m from InAsâˆ•GaAs quantum dots grown by antimony-mediated metal organic chemical vapor deposition. Applied Physics Letters, 2007, 90, 241110.	1.5	39
154	Spin-Related Current Suppression in a Semiconductor Quantum Dot Spin-Diode Structure. Physical Review Letters, 2009, 102, 236806.	2.9	39
155	High conductance bottom-contact pentacene thin-film transistors with gold-nickel adhesion layers. Applied Physics Letters, 2010, 97, 033306.	1.5	39
156	High Q H1 photonic crystal nanocavities with efficient vertical emission. Optics Express, 2012, 20, 28292.	1.7	39
157	Spontaneous Emission Characteristics of Quantum Well Lasers in Strong Magnetic Fields -- An Approach to Quantum-Well-Box Light Source --. Japanese Journal of Applied Physics, 1983, 22, L804-L806.	0.8	38
158	Two-Dimensional Photonic Crystal Resist Membrane Nanocavity Embedding Colloidal Dot-in-a-Rod Nanocrystals. Nano Letters, 2008, 8, 260-264.	4.5	38
159	Fabrication of AlGaN Two-Dimensional Photonic Crystal Nanocavities by Selective Thermal Decomposition of GaN. Applied Physics Express, 2012, 5, 126502.	1.1	38
160	Strongly Coupled Single-Quantum-Dotâ€"Cavity System Integrated on a CMOS-Processed Silicon Photonic Chip. Physical Review Applied, 2019, 11, .	1.5	38
161	Fabrication of verticalâ€microcavity quantum wire lasers. Applied Physics Letters, 1994, 64, 2200-2202.	1.5	37
162	Photoluminescence studies of GaAs quantum wires with quantum confined Stark effect. Applied Physics Letters, 1997, 70, 646-648.	1.5	37

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163	Optical add-drop multiplexers based on Si-wire waveguides. Applied Physics Letters, 2005, 86, 191107.	1.5	37
164	Strain-energy distribution and electronic structure of InAs pyramidal quantum dots with uncovered surfaces: Tight-binding analysis. Physical Review B, 1998, 57, 13016-13019.	1.1	36
165	Observation of enhanced spontaneous emission coupling factor in nitride-based vertical-cavity surface-emitting laser. Applied Physics Letters, 2002, 80, 722-724.	1.5	36
166	Thermooptic switch based on photonic-crystal line-defect waveguides. IEEE Photonics Technology Letters, 2005, 17, 2083-2085.	1.3	36
167	Growth of InAsâˆ•Sb:GaAs quantum dots on silicon substrate with high density and efficient light emission in the 1.3Î¼m band. Applied Physics Letters, 2008, 92, .	1.5	36
168	Demonstration of transverse-magnetic dominant gain in quantum dot semiconductor optical amplifiers. Applied Physics Letters, 2008, 92, .	1.5	36
169	Increase of Q-factor in photonic crystal H1-defect nanocavities after closing of photonic bandgap with optimal slab thickness. Optics Express, 2008, 16, 448.	1.7	36
170	Optical spectroscopy of self-assembled type II GaSb/GaAs quantum dot structures grown by molecular beam epitaxy. Applied Physics Letters, 1998, 72, 2856-2858.	1.5	35
171	Demonstration of high-Qâ€ˆ(>8600) three-dimensional photonic crystal nanocavity embedding quantum dots. Applied Physics Letters, 2009, 94, .	1.5	35
172	Polarization-Insensitive Quantum Dot Semiconductor Optical Amplifiers Using Strain-Controlled Columnar Quantum Dots. Journal of Lightwave Technology, 2012, 30, 68-75.	2.7	35
173	Polarization dependence of optoelectronic properties in quantum dots and quantum wires-consequences of valence-band mixing. IEEE Journal of Quantum Electronics, 1994, 30, 640-653.	1.0	34
174	Misorientation-angle dependence of GaN layers grown on a-plane sapphire substrates by metalorganic chemical vapor deposition. Applied Physics Letters, 2001, 79, 1992-1994.	1.5	34
175	Enhanced light emission from an organic photonic crystal with a nanocavity. Applied Physics Letters, 2005, 87, 151119.	1.5	34
176	Quantum-Dot Semiconductor Optical Amplifiers With Polarization-Independent Gains in 1.5-mum Wavelength Bands. IEEE Photonics Technology Letters, 2008, 20, 1908-1910.	1.3	34
177	Flexible thin-film InAs/GaAs quantum dot solar cells. Applied Physics Letters, 2012, 100, .	1.5	34
178	Molecular beam epitaxial growths of high-optical-gain InAs quantum dots on GaAs for long-wavelength emission. Journal of Crystal Growth, 2013, 378, 459-462.	0.7	34
179	Reduction of the spectral linewidth of semiconductor lasers with quantum wire effectsâ€"Spectral properties of GaAlAs double heterostructure lasers in high magnetic fields. Applied Physics Letters, 1986, 48, 384-386.	1.5	33
180	Observation of a single photoluminescence peak from a single quantum dot. Applied Physics Letters, 1995, 67, 3257-3259.	1.5	33

#	Article	IF	Citations
181	Magnetoresistance oscillations induced by intersubband scattering of two-dimensional electron gas in Al[sub 0.22]Ga[sub 0.78]N/GaN heterostructures. Journal of Applied Physics, 2003, 94, 5420.	1.1	33
182	Near band edge polarization dependence as a probe of structural symmetry in GaAs/AlGaAs quantum dot structures. Applied Physics Letters, 1993, 62, 756-758.	1.5	32
183	Saturation of photoluminescence quenching under below-gap excitation in a GaAs/AlGaAs quantum well. Journal of Luminescence, 1995, 63, 235-240.	1.5	32
184	Effect of antimony on the density of InAs/Sb:GaAs(100) quantum dots grown by metalorganic chemical-vapor deposition. Journal of Crystal Growth, 2007, 298, 548-552.	0.7	32
185	Effect of cavity mode volume on photoluminescence from silicon photonic crystal nanocavities. Applied Physics Letters, 2011, 98, .	1.5	32
186	Off-plane angle dependence of photonic band gap in a two-dimensional photonic crystal. IEEE Journal of Quantum Electronics, 1996, 32, 535-542.	1.0	31
187	Low-voltage-operating organic complementary circuits based on pentacene and C60 transistors. Thin Solid Films, 2009, 517, 2079-2082.	0.8	31
188	Cavity Quantum Electrodynamics and Lasing Oscillation in Single Quantum Dot-Photonic Crystal Nanocavity Coupled Systems. IEEE Journal of Selected Topics in Quantum Electronics, 2012, 18, 1818-1829.	1.9	31
189	Spectral diffusion in nitride quantum dots: Emission energy dependent linewidths broadening via giant builtâ€in dipole moments. Physica Status Solidi - Rapid Research Letters, 2014, 8, 408-413.	1.2	31
190	Vacuum Rabi Spectra of a Single Quantum Emitter. Physical Review Letters, 2015, 114, 143603.	2.9	31
191	Yellow luminescence band in undoped GaN revealed by two-wavelength excited photoluminescence. Optical Materials, 2016, 60, 481-486.	1.7	31
192	Microcavity-based generation of full PoincarÃ© beams with arbitrary skyrmion numbers. Physical Review Research, 2021, 3, .	1.3	31
193	Fabrication of InGaAs Strained Quantum Wire Structures Using Selective-Area Metal-Organic Chemical Vapor Deposition Growth. Japanese Journal of Applied Physics, 1993, 32, L1377-L1379.	0.8	30
194	Effect of carrier confinement on photoluminescence from modulation-doped AlxGa1â^'xN/GaN heterostructures. Applied Physics Letters, 2000, 76, 679-681.	1.5	30
195	Lasing characteristics of InAs quantum-dot microdisk from 3K to room temperature. Applied Physics Letters, 2004, 85, 1326-1328.	1.5	30
196	Soluble Polymer Complexes Having AlQ3-Type Pendent Groups. Macromolecular Rapid Communications, 2004, 25, 1171-1174.	2.0	30
197	Strain distribution and electronic states in stacked InAs/GaAs quantum dots with dot spacing 0â€". Physica E: Low-Dimensional Systems and Nanostructures, 2005, 26, 217-221.	1.3	30
198	Enhanced Luminance Efficiency of Organic Light-Emitting Diodes with Two-Dimensional Photonic Crystals. Japanese Journal of Applied Physics, 2005, 44, 2844-2848.	0.8	30

#	Article	IF	Citations
199	Quantum confined Stark effect in single self-assembled GaN/AlN quantum dots. Physica E: Low-Dimensional Systems and Nanostructures, 2006, 32, 148-151.	1.3	30
200	Interface properties of InAs quantum dots produced by antimony surfactant-mediated growth: Etching of segregated antimony and its impact on the photoluminescence and lasing characteristics. Applied Physics Letters, 2009, 94, .	1.5	30
201	Observation of mid-infrared intersubband absorption in non-polar m-plane AlGaN/GaN multiple quantum wells. Applied Physics Letters, 2014, 105, .	1.5	30
202	Nonlinear gain effects in quantum well, quantum well wire, and quantum well box lasers. IEEE Journal of Quantum Electronics, 1991, 27, 1824-1829.	1.0	29
203	Conformation and Local Environment Dependent Conductance of DNA Molecules. Small, 2005, 1, 1168-1172.	5.2	29
204	High-<i>Q</i> AlN photonic crystal nanobeam cavities fabricated by layer transfer. Applied Physics Letters, 2012, 101, .	1.5	29
205	Surface-passivated high-<i>Q</i> GaAs photonic crystal nanocavity with quantum dots. APL Photonics, 2020, 5, .	3.0	29
206	<i>In situ</i> wavelength tuning of quantum-dot single-photon sources integrated on a CMOS-processed silicon waveguide. Applied Physics Letters, 2020, 116, .	1.5	29
207	Process dependence of AlAs/GaAs superlattice mixing induced by silicon implantation. Applied Physics Letters, 1987, 50, 281-283.	1.5	28
208	Observation of a short optical pulse (<1.3 ps) from a gainâ€switched quantum well laser. Applied Physics Letters, 1988, 53, 1580-1582.	1.5	28
209	Light emission from individual self-assembled InAs/GaAs quantum dots excited by tunneling current injection. Applied Physics Letters, 1998, 73, 1460-1462.	1.5	28
210	High-performance pentacene thin-film transistors with high dielectric constant gate insulators. Applied Physics Letters, 2006, 89, 223525.	1.5	28
211	Vertical Microcavity Lasers with InGaAs/GaAs Quantum Dots Formed by Spinodal Phase Separation. Japanese Journal of Applied Physics, 1997, 36, L357-L360.	0.8	27
212	Seeded self-assembled GaAs quantum dots grown in two-dimensional V grooves by selective metalâ€“organic chemical-vapor deposition. Applied Physics Letters, 1998, 72, 800-802.	1.5	27
213	Organic Transistor Circuits for Application to Organic Light-Emitting-Diode Displays. Japanese Journal of Applied Physics, 2003, 42, 2483-2487.	0.8	27
214	Focusing characteristics of optical fiber axicon microlens for near-field spectroscopy: Dependence of tip apex angle. Optics Communications, 2006, 267, 264-270.	1.0	27
215	Highly efficient optical pumping of photonic crystal nanocavity lasers using cavity resonant excitation. Applied Physics Letters, 2006, 89, 161111.	1.5	27
216	Strong exciton confinement in site-controlled GaN quantum dots embedded in nanowires. Applied Physics Letters, 2013, 103, 171907.	1.5	27

#	Article	IF	Citations
217	Large vacuum Rabi splitting between a single quantum dot and an H0 photonic crystal nanocavity. Applied Physics Letters, 2018, 112, .	1.5	27
218	Dynamic and spectral properties of semiconductor lasers with quantum-well and quantum-wire effects. Surface Science, 1986, 174, 155-162.	0.8	26
219	Fabrication and optical properties of GaAs quantum wires and dots by MOCVD selective growth. Semiconductor Science and Technology, 1993, 8, 1082-1088.	1.0	26
220	Magnetic field dependence of exciton oscillator strength by measurements of magnetoexcitonâ€polariton mode splitting in quantum wells with a microcavity. Applied Physics Letters, 1996, 69, 887-889.	1.5	26
221	Measurement of an Exciton Rabi Rotation in a SingleGaN/AlxGa1âˆ'xNNanowire-Quantum Dot Using Photoluminescence Spectroscopy: Evidence for Coherent Control. Physical Review Letters, 2013, 111, 057401.	2.9	26
222	Highly uniform, multi-stacked InGaAs/GaAs quantum dots embedded in a GaAs nanowire. Applied Physics Letters, 2014, 105, .	1.5	26
223	InAs/GaAs Quantum Dot Lasers on Silicon-on-Insulator Substrates by Metal-Stripe Wafer Bonding. IEEE Photonics Technology Letters, 2015, 27, 875-878.	1.3	26
224	III-nitride quantum dots as single photon emitters. Semiconductor Science and Technology, 2019, 34, 033001.	1.0	26
225	Time-resolved photoluminescence of GaN/Al[sub 0.5]Ga[sub 0.5]N quantum wells. Applied Physics Letters, 2000, 77, 1005.	1.5	25
226	Two-photon absorption and multiphoton-induced photoluminescence of bulk GaN excited below the middle of the band gap. Applied Physics Letters, 2003, 82, 4714-4716.	1.5	25
227	Development of a Method for Preparing a Highly Reactive and Stable, Recyclable and Environmentally Benign Organopalladium Catalyst Supported on Sulfur-Terminated Gallium Arsenide(001): A Three-Component Catalyst, {Pd}-S-GaAs(001), and its Properties. Advanced Synthesis and Catalysis, 2006, 348, 1063-1070.	2.1	25
228	In SituScanning Tunneling Microscope Observation of InAs Wetting Layer Formation on GaAs(001) during Molecular Beam Epitaxy Growth at 500 Â°C. Japanese Journal of Applied Physics, 2006, 45, L777-L779.	0.8	25
229	Effects of rapid thermal annealing on the emission properties of highly uniform self-assembled InAsâˆ•GaAs quantum dots emitting at 1.3Î¼m. Applied Physics Letters, 2007, 90, 111912.	1.5	25
230	First Demonstration of Electrically Driven 1.55 Âµm Single-Photon Generator. Japanese Journal of Applied Physics, 2008, 47, 2880-2883.	0.8	25
231	Identification of electric dipole moments of excitonic complexes in nitride-based quantum dots. Physical Review B, 2013, 88, .	1.1	25
232	Direct Observation of Two-Step Photon Absorption in an InAs/GaAs Single Quantum Dot for the Operation of Intermediate-Band Solar Cells. Nano Letters, 2015, 15, 4483-4487.	4.5	25
233	Doping dependent blue shift and linewidth broadening of intersubband absorption in non-polar m-plane AlGaN/GaN multiple quantum wells. Applied Physics Letters, 2015, 107, .	1.5	25
234	Direct modulation of 13 Î¼m quantum dot lasers on silicon at 60 Â°C. Optics Express, 2016, 24, 18428.	1.7	25

#	Article	IF	Citations
235	Hot photoluminescence of GaAs-AlGaAs multiple quantum well structures under high excitation by a single shot of 30 ps, 532 nm laser. Solid State Communications, 1985, 55, 311-315.	0.9	24
236	Coherent and incoherent dynamics of excitons in semiconductor microcavities. Nuovo Cimento Della Societa Italiana Di Fisica D - Condensed Matter, Atomic, Molecular and Chemical Physics, Biophysics, 1995, 17, 1295-1303.	0.4	24
237	Formation of InGaAs Quantum Dots on GaAs Multi-Atomic Steps by Metalorganic Chemical Vapor Deposition Growth. Japanese Journal of Applied Physics, 1995, 34, 4376-4379.	0.8	24
238	Enhancement of the Coulomb correlations in type-II quantum dots. Physica E: Low-Dimensional Systems and Nanostructures, 2000, 7, 393-397.	1.3	24
239	Analysis of gain saturation in In0.02Ga0.98N/In0.16Ga0.84N multiple quantum wells. Applied Physics Letters, 2001, 79, 3434-3436.	1.5	24
240	Dynamics of single InGaN quantum dots. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 21, 285-289.	1.3	24
241	Biexciton and exciton dynamics in single InGaN quantum dots. Nanotechnology, 2005, 16, 1477-1481.	1.3	24
242	High performance flexible pentacene thin-film transistors fabricated on titanium silicon oxide gate dielectrics. Applied Physics Letters, 2007, 90, 163514.	1.5	24
243	Development of a two-dimensional dual pendulum thrust stand for Hall thrusters. Review of Scientific Instruments, 2007, 78, 115108.	0.6	24
244	Quantitative Estimation of Exchange Interaction Energy Using Two-Electron Vertical Double Quantum Dots. Physical Review Letters, 2009, 102, 146802.	2.9	24
245	High-Q (>5000) AlN nanobeam photonic crystal cavity embedding GaN quantum dots. Applied Physics Letters, 2012, 100, .	1.5	24
246	Site-controlled growth of single GaN quantum dots in nanowires by MOCVD. Journal of Crystal Growth, 2013, 370, 328-331.	0.7	24
247	Fermi energy dependence of linewidth enhancement factor of GaAlAs buried heterostructure lasers. Applied Physics Letters, 1985, 47, 905-907.	1.5	23
248	Growth of InGaN self-assembled quantum dots and their application to lasers. IEEE Journal of Selected Topics in Quantum Electronics, 2000, 6, 475-481.	1.9	23
249	Influence of Ferroelectric Polarization on the Properties of Two-Dimensional Electron Gas in Pb(Zr0.53Ti0.47)O3/AlxGa1-xN/GaN Structures. Japanese Journal of Applied Physics, 2002, 41, 2528-2530.	0.8	23
250	Improvement of the uniformity of self-assembled InAs quantum dots grown on InGaAsâˆ•GaAs by low-pressure metalorganic chemical vapor deposition. Applied Physics Letters, 2004, 85, 2753-2755.	1.5	23
251	Optical properties of columnar InAs quantum dots on InP for semiconductor optical amplifiers. Applied Physics Letters, 2008, 93, 121908.	1.5	23
252	Narrow spectral linewidth of single zinc-blende GaN/AlN self-assembled quantum dots. Applied Physics Letters, 2013, 103, 151109.	1.5	23

#	Article	IF	Citations
253	Giant optical rotation in a three-dimensional semiconductor chiral photonic crystal. Optics Express, 2013, 21, 29905.	1.7	23
254	Enhanced Single-Photon Emission from GaN Quantum Dots in Bullseye Structures. ACS Photonics, 2021, 8, 1656-1661.	3.2	23
255	Reduction of the field spectrum linewidth of a multiple quantum well laser in a high magnetic fieldâ€"spectral properties of quantum dot lasers. Applied Physics Letters, 1987, 50, 365-367.	1.5	22
256	Long-lived electron spins in InxGa1â^ˆ'xN multiquantum well. Applied Physics Letters, 2005, 86, 242103.	1.5	22
257	Heteroepitaxial growth of InAs on GaAs(001) by in situ STM located inside MBE growth chamber. Microelectronics Journal, 2006, 37, 1498-1504.	1.1	22
258	High performance n-channel thin-film transistors with an amorphous phase C60 film on plastic substrate. Applied Physics Letters, 2007, 91, .	1.5	22
259	Differential gain of GaAs/AlGaAs quantum well and modulationâ€doped quantum well lasers. Applied Physics Letters, 1991, 58, 4-6.	1.5	21
260	Fabrication of InGaAs strained quantum wires using selective MOCVD growth on SiO2-patterned GaAs substrate. Journal of Crystal Growth, 1992, 124, 502-506.	0.7	21
261	Demonstration of confined optical field effect in a vertical microcavity by examining the low temperature photonâ€exciton interaction in two kinds of quantum wells. Applied Physics Letters, 1994, 64, 1068-1070.	1.5	21
262	New SNOM sensor using optical feedback in a VCSEL-based compound-cavity. Sensors and Actuators A: Physical, 2001, 87, 113-123.	2.0	21
263	Near-field optical photoluminescence microscopy of high-density InAs/GaAs single quantum dots. Applied Physics Letters, 2002, 80, 2779-2781.	1.5	21
264	Formation of ultrahigh-density InAs/AlAs quantum dots by metalorganic chemical vapor deposition. Applied Physics Letters, 2004, 84, 1877-1879.	1.5	21
265	Enhancement of light emission from single quantum dot in photonic crystal nanocavity by using cavity resonant excitation. Applied Physics Letters, 2006, 89, 241124.	1.5	21
266	High-performance fullerene C60 thin-film transistors operating at low voltages. Applied Physics Letters, 2007, 91, 183514.	1.5	21
267	Ultra-low threshold photonic crystal nanocavity laser. Physica E: Low-Dimensional Systems and Nanostructures, 2008, 40, 1800-1803.	1.3	21
268	High performance inkjet-printed C60 fullerene thin-film transistors: Toward a low-cost and reproducible solution process. Organic Electronics, 2013, 14, 644-648.	1.4	21
269	Nanocavity-based self-frequency conversion laser. Optics Express, 2013, 21, 19778.	1.7	21
270	Fabrication and optical properties of non-polar III-nitride air-gap distributed Bragg reflector microcavities. Applied Physics Letters, 2013, 103, .	1.5	21

#	Article	IF	Citations
271	Selective growth of GaAs wire structures by electron beam induced metalorganic chemical vapor deposition. Applied Physics Letters, 1992, 60, 68-70.	1.5	20
272	Ultrashort lifetime photocarriers in Ge thin films. Applied Physics Letters, 1996, 68, 3419-3421.	1.5	20
273	Novel Palladium Catalyst Supported on GaAs(001) Passivated by Ammonium Sulfide. Chemistry Letters, 2004, 33, 1208-1209.	0.7	20
274	Tunable Optical Notch Filter Realized by Shifting the Photonic Bandgap in a Silicon Photonic Crystal Line-Defect Waveguide. IEEE Photonics Technology Letters, 2006, 18, 2614-2616.	1.3	20
275	Investigation of the Spectral Triplet in Strongly Coupled Quantum Dotâ€"Nanocavity System. Applied Physics Express, 2009, 2, 122301.	1.1	20
276	Strong coupling in non-polar GaN/AlGaN microcavities with air-gap/III-nitride distributed Bragg reflectors. Applied Physics Letters, 2015, 107, .	1.5	20
277	Spectral diffusion time scales in InGaN/GaN quantum dots. Applied Physics Letters, 2019, 114, .	1.5	20
278	Single-photon emission from isolated monolayer islands of InGaN. Light: Science and Applications, 2020, 9, 159.	7.7	20
279	Three-dimensional photonic crystal simultaneously integrating a nanocavity laser and waveguides. Optica, 2019, 6, 296.	4.8	20
280	Magnetoexcitons in quantum wires with an anisotropic parabolic potential. Physical Review B, 1994, 50, 7719-7723.	1.1	19
281	Microphotoluminescence spectroscopy of vertically stackedInxGa1â^'xAs/GaAsquantum wires. Physical Review B, 1998, 58, 1962-1966.	1.1	19
282	Near 1.3 ?m Emission at Room Temperature from InAsSb/GaAs Self-Assembled Quantum Dots on GaAs Substrates. Physica Status Solidi (B): Basic Research, 2001, 224, 139-142.	0.7	19
283	Zero-cell photonic crystal nanocavity laser with quantum dot gain. Applied Physics Letters, 2010, 97, .	1.5	19
284	A direct evidence of allocating yellow luminescence band in undoped GaN by two-wavelength excited photoluminescence. Applied Physics Letters, 2015, 107, .	1.5	19
285	Room-Temperature Observation of Trapped Exciton-Polariton Emission in GaN/AlGaN Microcavities with Air-Gap/III-Nitride Distributed Bragg Reflectors. ACS Photonics, 2016, 3, 1182-1187.	3.2	19
286	Improvement of single photon emission from InGaN QDs embedded in porous micropillars. Applied Physics Letters, 2018, 113, .	1.5	19
287	Electron-Hole Correlation in Quantum Dots under a High Magnetic Field (up to 45 T). Physical Review Letters, 1999, 83, 4832-4835.	2.9	18
288	Carrier relaxation in closely stacked InAs quantum dots. Journal of Applied Physics, 2004, 96, 150-154.	1.1	18

#	Article	IF	Citations
289	Controlling Polarization of 1.55-Âµm Columnar InAs Quantum Dots with Highly Tensile-Strained InGaAsP Barriers on InP(001). Japanese Journal of Applied Physics, 2006, 45, L1244-L1246.	0.8	18
290	Coherently driven semiconductor quantum dot at a telecommunication wavelength. Optics Express, 2008, 16, 13949.	1.7	18
291	Thin-film InAs/GaAs quantum dot solar cells layer-transferred onto Si substrates and flexible plastic films. , 2012, , .		18
292	Nanosecond-scale spectral diffusion in the single photon emission of a GaN quantum dot. AIP Advances, 2017, 7, .	0.6	18
293	Singleâ€photon emission from a further confined InGaN/GaN quantum disc via reverseâ€reaction growth. Quantum Engineering, 2019, 1, e20.	1.2	18
294	Modulation of Hepatocarcinoma Cell Morphology and Activity by Parylene-C Coating on PDMS. PLoS ONE, 2010, 5, e9667.	1.1	18
295	Tightâ€binding analysis of the conductionâ€band structure in quantum wires. Applied Physics Letters, 1990, 57, 1224-1226.	1.5	17
296	Quantum wires with strain effect: Tight-binding analysis. Surface Science, 1992, 267, 291-295.	0.8	17
297	Theoretical analysis of band structures and lasing characteristics in strained quantum wire lasers. IEEE Journal of Quantum Electronics, 1993, 29, 2109-2116.	1.0	17
298	Direct observation of the transition from a 2D layer to 3D islands at the initial stage of InGaAs growth on GaAs by AFM. Journal of Crystal Growth, 1997, 170, 563-567.	0.7	17
299	Photorefractive multiple quantum wells at 1064â€‰â€‰nm. Optics Letters, 2001, 26, 22.	1.7	17
300	Cyclotron resonance and magnetotransport measurements in AlxGa1â^'xN/GaN heterostructures for x=0.15â€"0.30. Applied Physics Letters, 2002, 80, 431-433.	1.5	17
301	InGaN Vertical Microcavity LEDs with a Si-Doped AlGaN/GaN Distributed Bragg Reflector. Physica Status Solidi A, 2002, 194, 403-406.	1.7	17
302	Multisubband transport of the two-dimensional electron gas in AlxGa1â^'xN/GaN heterostructures. Journal of Applied Physics, 2003, 93, 1651-1655.	1.1	17
303	Lasing at 1.28 /spl mu/m of InAs-GaAs quantum dots with AlGaAs cladding layer grown by metal-organic chemical vapor deposition. IEEE Journal of Selected Topics in Quantum Electronics, 2005, 11, 1027-1034.	1.9	17
304	CW Lasing at 1.35 mum From Ten InAsâ€"Sbâ€‰:â€‰GaAs Quantum-Dot Layers Grown by Metalâ€"Organic Chemical Vapor Deposition. IEEE Photonics Technology Letters, 2008, 20, 827-829.	1.3	17
305	Exciton dynamics in current-injected single quantum dot at 1.55Î¼m. Applied Physics Letters, 2008, 92, 161104.	1.5	17
306	Growth of high-uniformity InAsâˆ•GaAs quantum dots with ultralow density below 107cmâ^'2 and emission above 1.3Î¼m. Applied Physics Letters, 2008, 92, 163101.	1.5	17

#	Article	IF	Citations
307	Dual luminescence from organic/inorganic hybrid p-n junction light-emitting diodes. Applied Physics Letters, 2009, 94, .	1.5	17
308	Development of high-density single-mode polymer waveguides with low crosstalk for chip-to-chip optical interconnection. Optics Express, 2013, 21, 24231.	1.7	17
309	Position-controlled InP nanowires with 10â€“100â€‰<i>Î¼</i>m pitches using Au-deposited SiO2/InP patterned substrates. Applied Physics Letters, 2014, 104, .	1.5	17
310	Classification of Reflection High-Energy Electron Diffraction Pattern Using Machine Learning. Crystal Growth and Design, 2020, 20, 5289-5293.	1.4	17
311	Observation of enhanced lateral confinement of excitons in GaAs quantum wires with various sizes (7â€“30 nm) by magnetophotoluminescence measurements. Applied Physics Letters, 1995, 66, 2502-2504.	1.5	16
312	Terahertz Emission from Quantum Beats in Coupled Quantum Wells. Japanese Journal of Applied Physics, 1998, 37, 1643-1645.	0.8	16
313	Design and analysis of micromechanical tunable interferometers for WDM free-space optical interconnection. Journal of Lightwave Technology, 1999, 17, 19-25.	2.7	16
314	Transport properties of two-dimensional electron gas in different subbands in triangular quantum wells at AlxGa1â^'xN/GaN heterointerfaces. Applied Physics Letters, 2003, 82, 1872-1874.	1.5	16
315	Weak anti-localization of the two-dimensional electron gas in modulation-doped AlxGa1â^'xNâˆ•GaN heterostructures with two subbands occupation. Applied Physics Letters, 2004, 85, 3125-3127.	1.5	16
316	13 Î¼m InAs/GaAs quantum dot lasers on Si rib structures with current injection across direct-bonded GaAs/Si heterointerfaces. Optics Express, 2012, 20, B315.	1.7	16
317	Design of Si/SiO_2 micropillar cavities for Purcell-enhanced single photon emission at 155ÂÎ¼m from InAs/InP quantum dots. Optics Letters, 2013, 38, 3241.	1.7	16
318	Unidirectional output from a quantum-dot single-photon source hybrid integrated on silicon. Optics Express, 2021, 29, 37117.	1.7	16
319	Fast bistable wavelength switching characteristics in two-electrode distributed feedback laser. IEEE Photonics Technology Letters, 1990, 2, 109-110.	1.3	15
320	Tight binding analysis for quantum-wire lasers and quantum-wire infrared detectors. IEEE Journal of Quantum Electronics, 1991, 27, 1817-1823.	1.0	15
321	Defect Modes in Two-Dimensional Triangular Photonic Crystals. Japanese Journal of Applied Physics, 1997, 36, L120-L123.	0.8	15
322	Microphotoluminescence Intensity Images of InGaN Single Quantum Wells. Japanese Journal of Applied Physics, 1999, 38, L1216-L1218.	0.8	15
323	Formation of uniform 10-nm-scale InGaN quantum dots by selective MOCVD growth and their micro-photoluminescence intensity images. Journal of Crystal Growth, 2000, 221, 576-580.	0.7	15
324	Enhanced photon emission and absorption of single quantum dot in resonance with two modes in photonic crystal nanocavity. Applied Physics Letters, 2008, 93, 183114.	1.5	15

#	Article	IF	Citations
325	Method for generating a photonic NOON state with quantum dots in coupled nanocavities. Physical Review A, 2017, 96, .	1.0	15
326	Circularly Polarized Topological Edge States Derived from Optical Weyl Points in Semiconductor-Based Chiral Woodpile Photonic Crystals. Journal of the Physical Society of Japan, 2018, 87, 123401.	0.7	15
327	Quantum dot lasers for silicon photonics. Semiconductors and Semimetals, 2019, 101, 91-138.	0.4	15
328	Elimination of anti-phase boundaries in a GaAs layer directly-grown on an on-axis Si(001) substrate by optimizing an AlGaAs nucleation layer. Japanese Journal of Applied Physics, 2019, 58, SBBE07.	0.8	15
329	Single Plasmon Generation in an InAs/GaAs Quantum Dot in a Transfer-Printed Plasmonic Microring Resonator. ACS Photonics, 2019, 6, 1106-1110.	3.2	15
330	Exciton radiative lifetime in GaAs quantum wires grown by metalorganic chemicalâ€vapor selective growth. Applied Physics Letters, 1994, 64, 1564-1566.	1.5	14
331	UV Photoluminescence from Size-Controlled GaN Quantum Dots Grown by MOCVD. Physica Status Solidi A, 2002, 192, 33-38.	1.7	14
332	In situ scanning tunneling microscopy of InAs quantum dots on GaAs() during molecular beam epitaxial growth. Surface Science, 2003, 544, 234-240.	0.8	14
333	Strain-induced modifications of the electronic states of InGaAs quantum dots embedded in bowed airbridge structures. Journal of Applied Physics, 2003, 94, 6812-6817.	1.1	14
334	Localized excitation of InGaAs quantum dots by utilizing a photonic crystal nanocavity. Applied Physics Letters, 2006, 88, 141108.	1.5	14
335	Design of high-Q photonic crystal microcavities with a graded square lattice for application to quantum cascade lasers. Optics Express, 2008, 16, 21321.	1.7	14
336	Photonic band-edge micro lasers with quantum dot gain. Optics Express, 2009, 17, 640.	1.7	14
337	Spin dynamics of excited trion states in a single InAs quantum dot. Physical Review B, 2010, 81, .	1.1	14
338	Growth of high-density 1.06-Î¼m InGaAs/GaAs quantum dots for high gain lasers by molecular beamepitaxy. Journal of Crystal Growth, 2013, 378, 627-630.	0.7	14
339	Resonant photorefractive effect in InGaAs/GaAs multiple quantum wells. Optics Letters, 1999, 24, 321.	1.7	13
340	Photorefractive InGaAs/GaAs multiple quantum wells in the Franzâ€"Keldysh geometry. Journal of Applied Physics, 2001, 89, 5889-5896.	1.1	13
341	Long-wavelength luminescence from GaSb quantum dots grown on GaAs substrates. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 21, 275-278.	1.3	13
342	Advances in growth and optical properties of GaN-based quantum dots. Physica Status Solidi (A) Applications and Materials Science, 2006, 203, 3512-3522.	0.8	13

#	Article	IF	Citations
343	Development of Electrically Driven Single-Quantum-Dot Device at Optical Fiber Bands. Japanese Journal of Applied Physics, 2006, 45, 3621-3624.	0.8	13
344	Coulomb blockade in a self-assembled GaN quantum dot. Applied Physics Letters, 2007, 90, 162109.	1.5	13
345	Optimizing the GaAs capping layer growth of 1.3Î¼m InAs/GaAs quantum dots by a combined two-temperature and annealing process at low temperatures. Journal of Crystal Growth, 2008, 310, 5469-5472.	0.7	13
346	Formation of <i>m</i>-plane InGaN/GaN quantum dots using strain engineering of AlGaN/AlN interlayers. Applied Physics Letters, 2011, 99, .	1.5	13
347	Shortâ€channel, highâ€mobility organic thinâ€film transistors with alkylated dinaphthothienothiophene. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 1632-1635.	0.8	13
348	Growth of InGaAs/GaAs nanowire-quantum dots on AlGaAs/GaAs distributed Bragg reflectors for laser applications. Journal of Crystal Growth, 2017, 468, 144-148.	0.7	13
349	Optical coupling between atomically thin black phosphorus and a two dimensional photonic crystal nanocavity. Applied Physics Letters, 2017, 110, .	1.5	13
350	Circularly polarized vacuum field in three-dimensional chiral photonic crystals probed by quantum dot emission. Physical Review B, 2017, 96, .	1.1	13
351	Ohmic contact and interfacial reaction of Ti/Al/Pt/Au metallic multi-layers on n-AlxGa1âˆ'xN/GaN heterostructures. Optical Materials, 2003, 23, 197-201.	1.7	12
352	Observation of 1.55 Âµm Light Emission from InAs Quantum Dots in Photonic Crystal Microcavity. Japanese Journal of Applied Physics, 2005, 44, 2579-2583.	0.8	12
353	Ground state lasing at 1.30 Âµm from InAs/GaAs quantum dot lasers grown by metalâ€"organic chemical vapor deposition. Nanotechnology, 2010, 21, 105604.	1.3	12
354	Growth of InAs/GaAs quantum dots on Si, Ge/Si and germanium-on-insulator-on-silicon (GeOI) substrates emitting in the 1.3 Î¼m band for silicon photonics. Journal of Crystal Growth, 2011, 315, 114-118.	0.7	12
355	Novel Solution Process for High-Mobility C$_{60}$ Fullerene Field-Effect Transistors. Applied Physics Express, 2011, 4, 121602.	1.1	12
356	High guided modeâ€"cavity mode coupling for an efficient extraction of spontaneous emission of a single quantum dot embedded in a photonic crystal nanobeam cavity. Physical Review B, 2012, 86, .	1.1	12
357	Temperature dependence of the single photon emission from interface-fluctuation GaN quantum dots. Scientific Reports, 2017, 7, 16107.	1.6	12
358	Nonlinear gain effects on spectral dynamics in quantum well lasers. IEEE Photonics Technology Letters, 1991, 3, 106-107.	1.3	11
359	High-resolution near-field spectroscopy of InAs single quantum dots at 70 K. Applied Physics Letters, 2003, 83, 3024-3026.	1.5	11
360	Single InAs/InP quantum dot spectroscopy in 1.3â€"1.55Î¼m telecommunication band. Physica E: Low-Dimensional Systems and Nanostructures, 2005, 26, 185-189.	1.3	11

#	Article	IF	Citations
361	Optical Polarization Properties of InAs/GaAs Quantum Dot Semiconductor Optical Amplifier. Japanese Journal of Applied Physics, 2005, 44, 2528-2530.	0.8	11
362	Internal Strain of Self-Assembled InxGa1-xAs Quantum Dots Calculated to Realize Transverse-Magnetic-Mode-Sensitive Interband Optical Transition at Wavelengths of 1.5 Âµm bands. Japanese Journal of Applied Physics, 2005, 44, 6312-6316.	0.8	11
363	Cavity Resonant Excitation of InGaAs Quantum Dots in Photonic Crystal Nanocavities. Japanese Journal of Applied Physics, 2006, 45, 6091-6095.	0.8	11
364	Effects of accumulated strain on the surface and optical properties of stacked 1.3Î¼m InAs/GaAs quantum dot structures. Physica E: Low-Dimensional Systems and Nanostructures, 2008, 40, 2182-2184.	1.3	11
365	Tunneling magnetoresistance effect in a few-electron quantum-dot spin valve. Applied Physics Letters, 2008, 93, 222107.	1.5	11
366	Suppression of indefinite peaks in InAs/GaAs quantum dot spectrum by low temperature capping in the indium-flush method. Physica E: Low-Dimensional Systems and Nanostructures, 2010, 42, 2753-2756.	1.3	11
367	Novel III-V/Si hybrid laser structures with current injection across conductive wafer-bonded heterointerfaces: A proposal and analysis. IEICE Electronics Express, 2011, 8, 596-603.	0.3	11
368	Improved stability in N-alkylated organic semiconductors for thin film transistors: Synthesis and characterization of N,Nâ€²-dialkylated dihydrodiazapentacene derivatives. Synthetic Metals, 2012, 162, 1264-1270.	2.1	11
369	Differential receivers with highly -uniform MSM Germanium photodetectors capped by SiGe layer. Optics Express, 2013, 21, 23295.	1.7	11
370	Photoluminescence Excitation Spectroscopy on Single GaN Quantum Dots. Applied Physics Express, 2013, 6, 012102.	1.1	11
371	Measuring the second-order coherence of a nanolaser by intracavity frequency doubling. Physical Review A, 2014, 89, .	1.0	11
372	Single photon source based on an InGaN quantum dot in a site-controlled optical horn structure. Applied Physics Letters, 2019, 115, .	1.5	11
373	GaAs-based microelectromechanical terahertz bolometers fabricated on high-resistivity Si substrates using wafer bonding technique. Applied Physics Letters, 2021, 119, .	1.5	11
374	Picosecond pulse generation in detuned distributed feedback lasers. Electronics Letters, 1988, 24, 170.	0.5	11
375	Transmission electron microscopy and photoluminescence study of silicon and boron ion implanted GaAs/GaAlAs quantum wells. Applied Physics Letters, 1987, 50, 92-94.	1.5	10
376	Picosecond lasing dynamics of gain-switched quantum well lasers and its dependence on quantum well structures. IEEE Journal of Quantum Electronics, 1991, 27, 1648-1654.	1.0	10
377	Highly uniform InGaAs quantum dots (â‰ˆ nm) grown by MOVPE on GaAs. Journal of Crystal Growth, 1994, 145, 986-987.	0.7	10
378	Microprobe spectroscopy of localized exciton states in IIâ€"VI quantum wells. Applied Physics Letters, 1998, 73, 148-150.	1.5	10

#	Article	IF	Citations
379	Below-Gap Spectroscopy of Undoped GaAs/AlGaAs Quantum Wells by Two-Wavelength Excited Photoluminescence. Japanese Journal of Applied Physics, 1998, 37, 3210-3213.	0.8	10
380	Highly Reactive Organopalladium Catalyst Formed on Sulfur-Terminated GaAs(001)-(2 Ã— 6) Surface. Japanese Journal of Applied Physics, 2006, 45, L475-L477.	0.8	10
381	Dislocation reduction of GaSb on GaAs by metalorganic chemical vapor deposition with epitaxial lateral overgrowth. Journal of Crystal Growth, 2008, 310, 4843-4845.	0.7	10
382	Switching operation of lasing wavelength in mid-infrared ridge-waveguide quantum cascade lasers coupled with microcylindrical cavity. Applied Physics Letters, 2010, 96, .	1.5	10
383	1064-nm DFB laser diode modules applicable to seeder for pulse-on-demand fiber laser systems. Optical Fiber Technology, 2014, 20, 714-724.	1.4	10
384	Probing the Excitonic States of Site-Controlled GaN Nanowire Quantum Dots. Nano Letters, 2015, 15, 1047-1051.	4.5	10
385	High quality-factor Si/SiO_2-InP hybrid micropillar cavities with submicrometer diameter for 155-Î¼m telecommunication band. Optics Express, 2015, 23, 16264.	1.7	10
386	Reflectivity of three-dimensional GaAs photonic band-gap crystals of finite thickness. Physical Review B, 2020, 101, .	1.1	10
387	Chiral modes near exceptional points in symmetry broken H1 photonic crystal cavities. Physical Review Research, 2021, 3, .	1.3	10
388	Fabrication and microscopic photoluminescence imaging of ridgeâ€type InGaAs quantum wires grown on a (110) cleaved plane of AlGaAs/GaAs superlattice. Applied Physics Letters, 1996, 69, 1294-1296.	1.5	9
389	Distribution of below-gap states in undoped GaAs/AlGaAs quantum wells revealed by two-wavelength excited photoluminescence. Journal of Luminescence, 1998, 79, 39-46.	1.5	9
390	Near-field optical spectroscopy of self-assembled quantum dots: NSOM apparatus for measuring the features of single dots. Solid-State Electronics, 1998, 42, 1083-1086.	0.8	9
391	Lifetime of Confined LO Phonons in Quantum Dots and Its Impact on Phonon Bottleneck Issue. Japanese Journal of Applied Physics, 1999, 38, 473-476.	0.8	9
392	Photoluminescence from sub-nanometer-thick GaN/Al0.8Ga0.2N quantum wells. Applied Physics Letters, 2000, 77, 1336-1338.	1.5	9
393	Uniform Array of GaN Quantum Dots in AlGaN Matrix by Selective MOCVD Growth. Physica Status Solidi (B): Basic Research, 2001, 228, 187-190.	0.7	9
394	Optical anisotropy of self-assembled InGaAs quantum dots embedded in wall-shaped and air-bridge structures. Applied Physics Letters, 2002, 81, 3954-3956.	1.5	9
395	Group-Delay Properties of Coupled-Defect Structures in Photonic Crystals. Japanese Journal of Applied Physics, 2004, 43, L449-L452.	0.8	9
396	Surface reconstructions on Sb-irradiated GaAs(001) formed by molecular beam epitaxy. Microelectronics Journal, 2007, 38, 620-624.	1.1	9

#	Article	IF	Citations
397	Enhancement of Valence Band Mixing in Individual InAs/GaAs Quantum Dots by Rapid Thermal Annealing. Japanese Journal of Applied Physics, 2013, 52, 125001.	0.8	9
398	Polarization properties of single zinc-blende GaN/AlN quantum dots. Physical Review B, 2014, 90, .	1.1	9
399	Excitonic complexes in single zinc-blende GaN/AlN quantum dots grown by droplet epitaxy. Applied Physics Letters, 2014, 105, .	1.5	9
400	Eigenvalue decomposition method for photon statistics of frequency-filtered fields and its application to quantum dot emitters. Physical Review A, 2015, 92, .	1.0	9
401	InAs/GaAs quantum dot infrared photodetectors on onâ€axis Si (100) substrates. Electronics Letters, 2018, 54, 1395-1397.	0.5	9
402	Evaluation of degradation behavior in quantum dot light-emitting diode with different hole transport materials via transient electroluminescence. Applied Physics Letters, 2021, 118, .	1.5	9
403	Picosecond spectral dynamics of gainâ€switched quantumâ€well lasers and its dependence on quantumâ€well structures. Journal of Applied Physics, 1990, 67, 2675-2677.	1.1	8
404	Theoretical analysis of bistable distributed feedback lasers with detuning effect. Journal of Lightwave Technology, 1990, 8, 1630-1637.	2.7	8
405	Dependence of lasing characteristics of quantum well lasers on substrate orientation: Tightâ€binding theory. Applied Physics Letters, 1991, 58, 881-883.	1.5	8
406	Phototransistors Using Point Contact Structures. Japanese Journal of Applied Physics, 1997, 36, 1955-1957.	0.8	8
407	Up-conversion luminescence via a below-gap state in GaAs/AlGaAs quantum wells. Superlattices and Microstructures, 1997, 22, 521-527.	1.4	8
408	Dielectric function associated with dispersive optic-vibrations. Solid State Communications, 1998, 108, 211-213.	0.9	8
409	Growth Condition Dependence of the Photoluminescence Properties of InxGa1-xN/InyGa1-yN Multiple Quantum Wells Grown by MOCVD. Japanese Journal of Applied Physics, 1999, 38, 2613-2616.	0.8	8
410	Growth and Structural Characterization of InGaN Vertical Cavity Surface Emitting Lasers Operating at Room Temperature. Physica Status Solidi A, 1999, 176, 63-66.	1.7	8
411	Photoluminescence of GaN Quantum Wells with AlGaN Barriers of High Aluminium Content. Physica Status Solidi A, 2000, 180, 339-343.	1.7	8
412	Nondegenerate pump and probe spectroscopy in InGaN thin films. Journal of Applied Physics, 2003, 94, 6468-6471.	1.1	8
413	Enhancement of Cavity-Qin a Quasi-Three-Dimensional Photonic Crystal. Japanese Journal of Applied Physics, 2004, 43, 1990-1994.	0.8	8
414	Manipulation of electronic states in single quantum dots by micromachined air-bridge. Applied Physics Letters, 2004, 84, 1392-1394.	1.5	8

#	Article	IF	Citations
415	Simultaneous determination of the index and absorption gratings in multiple quantum well photorefractive devices designed for laser ultrasonic sensor. Optics Communications, 2004, 242, 7-12.	1.0	8
416	Growth of Columnar Quantum Dots by Metalorganic Vapor-Phase Epitaxy for Semiconductor Optical Amplifiers. Japanese Journal of Applied Physics, 2008, 47, 2888-2892.	0.8	8
417	Enhancement of photoluminescence from germanium by utilizing air-bridge-type photonic crystal slab. Physica E: Low-Dimensional Systems and Nanostructures, 2010, 42, 2556-2559.	1.3	8
418	Silicon-based three-dimensional photonic crystal nanocavity laser with InAs quantum-dot gain. Applied Physics Letters, 2012, 101, .	1.5	8
419	Shaking quantum dots. Nature Photonics, 2012, 6, 9-10.	15.6	8
420	Asymmetric out-of-plane power distribution in a two-dimensional photonic crystal nanocavity. Optics Letters, 2015, 40, 3372.	1.7	8
421	InAs/GaAs quantum dot lasers with GaP strain-compensation layers grown by molecular beam epitaxy. Physica Status Solidi (A) Applications and Materials Science, 2016, 213, 958-964.	0.8	8
422	Low-Noise Characteristics on 1.3-Î¼m-Wavelength Quantum-Dot DFB Lasers Under External Optical Feedback. , 2018, , .		8
423	Pure single-photon emission from an InGaN/GaN quantum dot. APL Materials, 2021, 9, .	2.2	8
424	Scheme for media conversion between electronic spin and photonic orbital angular momentum based on photonic nanocavity. Optics Express, 2018, 26, 21219.	1.7	8
425	A large-scale single-mode array laser based on a topological edge mode. Nanophotonics, 2022, 11, 2169-2181.	2.9	8
426	Cavity optimization for minimum pulsewidth of gain-switched semiconductor lasers. IEEE Photonics Technology Letters, 1995, 7, 272-274.	1.3	7
427	Time and spatial resolved photoluminescence from a single quantum dot. Solid-State Electronics, 1996, 40, 537-540.	0.8	7
428	Light emission from vertical-microcavity quantum dot laser structures. Physica B: Condensed Matter, 1996, 227, 404-406.	1.3	7
429	Near-field spectroscopy of a single InGaAs self-assembled quantum dot. IEEE Journal of Selected Topics in Quantum Electronics, 2000, 6, 528-533.	1.9	7
430	Observation of Intersubband Transition from the First to the Third Subband (e1-e3) in GaN/AlGaN Quantum Wells. Physica Status Solidi A, 2002, 192, 27-32.	1.7	7
431	Stranskiâ€“Krastanow growth of stacked GaN quantum dots with intense photoluminescence. Physica Status Solidi (B): Basic Research, 2003, 240, 322-325.	0.7	7
432	Polarization field and electronic states of GaN pyramidal quantum dots in AlN. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 1169-1172.	0.8	7

#	Article	IF	Citations
433	Picosecond dynamics of spin-related optical nonlinearities in InxGa1â^'xAs multiple quantum wells at 1064 nm. Applied Physics Letters, 2004, 84, 1043-1045.	1.5	7
434	Structural and optical properties of high-density (>1011/cm2) InAs QDs with varying Al(Ga)As matrix layer thickness. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 21, 279-284.	1.3	7
435	Spin and carrier relaxation in resonantly excited InGaAs MQWs. Semiconductor Science and Technology, 2004, 19, S339-S341.	1.0	7
436	Lowâ€voltageâ€operating fullerene C₆₀ thinâ€film transistors with various surface treatments. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 3181-3183.	0.8	7
437	Resonant photoluminescence from Ge self-assembled dots in optical microcavities. Journal of Crystal Growth, 2009, 311, 883-887.	0.7	7
438	AlGaAs capping effect on InAs quantum dots self-assembled on GaAs. Physics Letters, Section A: General, Atomic and Solid State Physics, 2011, 375, 3517-3520.	0.9	7
439	Fabrication of electrically pumped InAs/GaAs quantum dot lasers on Si substrates by Auâ€mediated wafer bonding. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 319-321.	0.8	7
440	Effects of growth temperature of partial GaAs cap on InAs quantum dots in Inâ€flush process for single dot spectroscopy. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 248-250.	0.8	7
441	Self-frequency summing in quantum dot photonic crystal nanocavity lasers. Applied Physics Letters, 2013, 103, 243115.	1.5	7
442	Emission at 1.6â€‰Î¼m from InAs Quantum Dots in Metamorphic InGaAs Matrix. Physica Status Solidi (B): Basic Research, 2020, 257, 1900392.	0.7	7
443	Photoelectrochemical investigation of charge injection efficiency for quantum dot light-emitting diode. Applied Physics Letters, 2021, 118, .	1.5	7
444	InAs/InGaAs Quantum Dot Lasers on Multi-Functional Metamorphic Buffer Layers. Optics Express, 2021, 29, 29378.	1.7	7
445	In situpatterning of contamination resists in metalorganic chemical vapor deposition for fabrication of quantum wires. Applied Physics Letters, 1991, 58, 2372-2374.	1.5	6
446	MOCVD selective growth of GaAs: C wire and dot structures by electron beam irradiation. Journal of Crystal Growth, 1992, 124, 213-219.	0.7	6
447	Optical properties of GaAs quantum dots fabricated by MOCVD selective growth. Solid-State Electronics, 1994, 37, 579-581.	0.8	6
448	Direct Observation of Electron Jet from a Point Contact. Japanese Journal of Applied Physics, 1996, 35, 1151-1153.	0.8	6
449	MOCVD Growth and Optical Characterization of Stacked InGaN Quantum Dots for Laser Applications. Physica Status Solidi A, 1999, 176, 629-633.	1.7	6
450	Absence of nonradiative recombination centers in modulation-doped quantum wells revealed by two-wavelength excited photoluminescence. Physica E: Low-Dimensional Systems and Nanostructures, 2000, 7, 563-566.	1.3	6

#	Article	IF	Citations
451	Investigation of the Polarization-Induced Charges in Modulation-Doped AlxGa1-xN/GaN Heterostructures through Capacitanceâ€"Voltage Profiling and Simulation. Japanese Journal of Applied Physics, 2002, 41, 2531-2535.	0.8	6
452	Optical Characteristics of Two-Dimensional Photonic Crystal Slab Nanocavities with Self-Assembled InAs Quantum Dots for 1.3 Âµm Light Emission. Japanese Journal of Applied Physics, 2003, 42, 2391-2394.	0.8	6
453	Formation of high-density GaN self-assembled quantum dots by MOCVD. Journal of Crystal Growth, 2004, 272, 161-166.	0.7	6
454	Telecom singleâ€photon source with horn structure. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 2699-2703.	0.8	6
455	Proton radiation effects in quantum dot lasers. Applied Surface Science, 2008, 255, 676-678.	3.1	6
456	Electric field modulation of exciton recombination in InAs/GaAs quantum dots emitting at 1.3Î¼m. Journal of Applied Physics, 2008, 104, 013504.	1.1	6
457	Charged and neutral biexcitonâ€"exciton cascade in a single quantum dot within a photonic bandgap. Physica E: Low-Dimensional Systems and Nanostructures, 2010, 42, 2563-2566.	1.3	6
458	Influence of p-doping on the temperature dependence of InAs/GaAs quantum dot excited state radiative lifetime. Applied Physics Letters, 2012, 101, .	1.5	6
459	Selfâ€assembled <i>m</i> â€plane InGaN quantum dots: formation and shape evolution. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 613-615.	0.8	6
460	Theoretical analysis of multilevel intermediate-band solar cells using a drift diffusion model. Journal of Applied Physics, 2013, 113, 243102.	1.1	6
461	Temperature Dependent Photoluminescence Excitation Spectroscopy of GaN Quantum Dots in Site Controlled GaN/AlGaN Nanowires. Japanese Journal of Applied Physics, 2013, 52, 08JL02.	0.8	6
462	Growth of highâ€quality InAs quantum dots embedded in GaAs nanowire structures on Si substrates. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 1496-1499.	0.8	6
463	Multi-channel Hybrid Integrated Light Source for Ultra-high-bandwidth Optical Interconnections and Its Structural Optimization for Low Power Consumption by Considering Thermal Interference between LD Arrays. Transactions of the Japan Institute of Electronics Packaging, 2014, 7, 94-103.	0.3	6
464	Effect of lateral electric field on the transition energies of neutral and charged excitons in<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:msub><mml:mi mathvariant="normal">In</mml:mi><mml:mrow><mml:mn>0.5</mml:mn></mml:mrow></mml:msub><mml:msub><mml:mi mathvariant="normal">Ga</mml:mi><mml:mrow><mml:mn>0.5</mml:mn></mml:mrow></mml:msub><mml:mi mathvariant="normal">As</mml:mi><mml:mo>/</mml:mo><mml:mi mathvariant="normal">GaAs</mml:mi></mml:math>quantum dots. Physical Review B, 2015, 91, .	1.1	6
465	Semiconductor Three-Dimensional Photonic Crystals with Novel Layer-by-Layer Structures. Photonics, 2016, 3, 34.	0.9	6
466	Highâ€•<i>Q</i> nanocavities in semiconductorâ€based threeâ€dimensional photonic crystals. Electronics Letters, 2018, 54, 305-307.	0.5	6
467	Fabrication and optical characterization of photonic crystal nanocavities with electrodes for gate-defined quantum dots. Japanese Journal of Applied Physics, 2020, 59, SGGI05.	0.8	6
468	Cross Sectional Shape Dependence of Quantum Wire Band Structures and Optical Matrix Elements. Japanese Journal of Applied Physics, 1993, 32, L1592-L1595.	0.8	5

#	Article	IF	Citations
469	Radiative lifetime of localized excitons in GaAs quantum dots. Superlattices and Microstructures, 1995, 17, 73-76.	1.4	5
470	Influence of AlxGa1â€"xN Thickness on Transport Properties of a Two-Dimensional Electron Gas in Modulation Doped AlxGa1â€"xN/GaN Single Heterostructures. Physica Status Solidi (B): Basic Research, 1999, 216, 755-759.	0.7	5
471	Characterization of Proton-Irradiated InGaAs/GaAs Multiple Quantum Well Structures by Nonresonant Transient Four-Wave Mixing Technique. Japanese Journal of Applied Physics, 2000, 39, 5781-5787.	0.8	5
472	InGaAs/GaAs photorefractive multiple quantum well device in quantum confined Stark geometry. Applied Physics B: Lasers and Optics, 2001, 72, 685-689.	1.1	5
473	Growth of InAs/GaAs quantum dots on germanium-on-insulator-on-silicon substrate for silicon photonics. Physica E: Low-Dimensional Systems and Nanostructures, 2010, 42, 2765-2767.	1.3	5
474	Competing influence of an in-plane electric field on the Stark shifts in a semiconductor quantum dot. Applied Physics Letters, 2011, 99, 181109.	1.5	5
475	Metal Organic Chemical Vapor Deposition Growth of High Spectral Quality Site-Controlled InAs Quantum Dots Using<i>In situ</i>Patterning. Applied Physics Express, 2011, 4, 112001.	1.1	5
476	Spectral fluctuations of excitonic transitions of InGaAs single quantum dots. Applied Physics Letters, 2012, 100, 022105.	1.5	5
477	Enhancement of Light Emission from Silicon by Utilizing Photonic Nanostructures. IEICE Transactions on Electronics, 2012, E95-C, 206-212.	0.3	5
478	Formation and optical properties of multi-stack InGaAs quantum dots embedded in GaAs nanowires by selective metalorganic chemical vapor deposition. Journal of Crystal Growth, 2013, 370, 299-302.	0.7	5
479	Highâ€‹<i>Q</i> AlN ladderâ€structure photonic crystal nanocavity fabricated by layer transfer. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 1517-1520.	0.8	5
480	Impact of the dark path on quantum dot single photon emitters in small cavities. Physical Review Letters, 2014, 113, 143604.	2.9	5
481	Quantum Dot Laser for a Light Source of an Athermal Silicon Optical Interposer. Photonics, 2015, 2, 355-364.	0.9	5
482	Demonstration of lasing oscillation in a plasmonic microring resonator containing quantum dots fabricated by transfer printing. Japanese Journal of Applied Physics, 2017, 56, 102001.	0.8	5
483	Double-stage guided-mode converter for pure TM-mode guiding in pillar photonic-crystal waveguide devices. Optics Express, 2017, 25, 17995.	1.7	5
484	Measurement of the Emission Lifetime of a GaN Interface Fluctuation Quantum Dot by Power Dependent Single Photon Dynamics. Physica Status Solidi (A) Applications and Materials Science, 2018, 215, 1700630.	0.8	5
485	Two-dimensional quantum-mechanical confinement of electrons in LED by strong magnetic fields. IEEE Transactions on Electron Devices, 1983, 30, 330-334.	1.6	4
486	Two-dimensional quantum-mechanical confinement of electrons in DH lasers by strong magnetic fields. IEEE Journal of Quantum Electronics, 1983, 19, 1255-1257.	1.0	4

#	Article	IF	Citations
487	Highâ€speed GaAs/AlGaAs photoconductive detector using apâ€modulationâ€doped multiquantum well structure. Applied Physics Letters, 1986, 48, 1096-1097.	1.5	4
488	Tight binding analysis of quantum wire structures. Superlattices and Microstructures, 1991, 10, 83-87.	1.4	4
489	Picosecond dynamics in gainâ€switched uncoupled and coupled quantum well lasers. Applied Physics Letters, 1991, 58, 2064-2066.	1.5	4
490	Consequences of structural disorder on laser properties in quantum wire lasers. IEEE Photonics Technology Letters, 1992, 4, 835-837.	1.3	4
491	MOCVD growth of a stacked InGaN quantum dot structure and its lasing oscillation at room temperature. Physica E: Low-Dimensional Systems and Nanostructures, 2000, 7, 944-948.	1.3	4
492	Area-Controlled Growth of InAs Quantum Dots by Selective MOCVD. Japanese Journal of Applied Physics, 2000, 39, 2344-2346.	0.8	4
493	Structure Dependence of Electron Mobility in GaN/AlGaN Multiple Quantum Wells. Physica Status Solidi A, 2001, 188, 877-880.	1.7	4
494	Line Broadening of Photoluminescence Excitation Resonances in Single Self-Assembled Quantum Dots. Japanese Journal of Applied Physics, 2002, 41, L1464-L1466.	0.8	4
495	Effect of thermal treatment on structure of GaN self-assembled quantum dots grown by MOCVD. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 1101-1104.	0.8	4
496	Enhanced Optical Properties of High-Density (>1011/cm2) InAs/AlAs Quantum Dots by Hydrogen Passivation. Japanese Journal of Applied Physics, 2004, 43, 2118-2121.	0.8	4
497	InAs/AlAs quantum dots with InGaAs insertion layer: dependence of the indium composition and the thickness. Physica E: Low-Dimensional Systems and Nanostructures, 2005, 26, 138-142.	1.3	4
498	Dispersion Compensation in 40 Gb/s Non-Return-to-Zero Optical Transmission System Using Coupled-Cavity Photonic Crystals. Japanese Journal of Applied Physics, 2005, 44, L1282-L1284.	0.8	4
499	40-Gbit/s Operation of Ultracompact Photodetector-Integrated Dispersion Compensator Based on One-Dimensional Photonic Crystals. Japanese Journal of Applied Physics, 2008, 47, 6672-6674.	0.8	4
500	InAs/Sb∶GaAs quantum dot solar cells grown by metal organic chemical vapor deposition. , 2009, , .		4
501	Synthesis and investigation of Ï€-conjugated azomethine self-assembled multilayers by layer-by-layer growth. Thin Solid Films, 2010, 518, 5115-5120.	0.8	4
502	Design of a highâ€Q H0 photonic crystal nanocavity for cavity QED. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 340-342.	0.8	4
503	Dominant nonradiative centers in InGaN single quantum well by timeâ€resolved and twoâ€wavelength excited photoluminescence. Physica Status Solidi (B): Basic Research, 2015, 252, 952-955.	0.7	4
504	Electroluminescence at 1.3 Âµm from InAs/GaAs quantum dots monolithically grown on Ge/Si substrate by metal organic chemical vapor deposition. Japanese Journal of Applied Physics, 2016, 55, 100304.	0.8	4

#	Article	IF	Citations
505	Linearly polarized single photons from small site-controlled GaN nanowire quantum dots. , 2016, , .		4
506	Impact of quantum dots on III-nitride lasers: a theoretical calculation of threshold current densities. Japanese Journal of Applied Physics, 2019, 58, SCCC31.	0.8	4
507	Classification of in situ reflection high energy electron diffraction images by principal component analysis. Japanese Journal of Applied Physics, 2021, 60, SBBK03.	0.8	4
508	Eâ€band InAs quantum dot laser on InGaAs metamorphic buffer layer with filter layer. Electronics Letters, 2021, 57, 567-568.	0.5	4
509	Characteristics of Double-Heterostructure Lasers in Strong Magnetic Fields. Japanese Journal of Applied Physics, 1983, 22, 283.	0.8	4
510	Ultrafast spectroscopy of carriers and excitons in semiconductor microcavities. Progress in Crystal Growth and Characterization of Materials, 1996, 33, 155-160.	1.8	3
511	Near-field spectroscopy of quantum wires grown by selective growth method. Physica E: Low-Dimensional Systems and Nanostructures, 1998, 2, 987-990.	1.3	3
512	Screening of the Polarization Field in InGaN Single Quantum Wells. Physica Status Solidi (B): Basic Research, 1999, 216, 423-426.	0.7	3
513	Influence of Coulomb and Exchange Interaction on Quantum Dot Magnetoluminescence up to B = 45 T. Physica Status Solidi A, 2000, 178, 263-268.	1.7	3
514	Resonant Raman scattering of optical phonons in self-assembled quantum dots. Physica E: Low-Dimensional Systems and Nanostructures, 2000, 8, 328-332.	1.3	3
515	Differential Absorption in InGaN Multiple Quantum Wells and Epilayers Induced by Blue-Violet Laser Diode. Japanese Journal of Applied Physics, 2004, 43, L340-L342.	0.8	3
516	Numerical analysis of DFB lasing action in photonic crystals with quantum dots. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 21, 814-819.	1.3	3
517	UV photoluminescence from GaN self-assembled quantum dots on AlxGa1â€“xN surfaces grown by metalorganic chemical vapor deposition. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 2516-2519.	0.8	3
518	Spectroscopy on single columns of vertically aligned InAs quantum dots. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 21, 409-413.	1.3	3
519	Optical Control of Transmittance by Photo-Induced Absorption Effect in InGaN/GaN Structures. Japanese Journal of Applied Physics, 2005, 44, 7238-7243.	0.8	3
520	Three-Dimensional Imaging of GaN Films Using Transient Two-Photon Absorption Excited by Near-Infrared Laser Pulses. Japanese Journal of Applied Physics, 2005, 44, L535-L538.	0.8	3
521	Development of high-yield fabrication technique for MEMS-PhC devices. IEICE Electronics Express, 2006, 3, 39-43.	0.3	3
522	Degenerate four-wave mixing spectroscopy of GaN films on various substrates. Physica Status Solidi (B): Basic Research, 2006, 243, 1560-1563.	0.7	3

#	Article	IF	Citations
523	Transient pumpâ€"probe measurements for polarized excitons in strained GaN epitaxial layers. Physica Status Solidi (B): Basic Research, 2006, 243, 1564-1567.	0.7	3
524	Advances in photonic crystals with MEMS and with semiconductor quantum dots. Laser Physics, 2006, 16, 223-231.	0.6	3
525	Elastic and inelastic tunneling through oneâ€electron and twoâ€electron states in a vertical double quantum dot. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 2854-2857.	0.8	3
526	Singletâ€"triplet transition induced by Zeeman energy in weakly coupled vertical double quantum dots. Physica E: Low-Dimensional Systems and Nanostructures, 2008, 40, 1139-1141.	1.3	3
527	Observation of unique photon statistics of single artificial atom laser. Physica E: Low-Dimensional Systems and Nanostructures, 2010, 42, 2489-2492.	1.3	3
528	Non-VLS growth of GaAs nanowires on silicon by a gallium pre-deposition technique. Journal of Crystal Growth, 2013, 378, 562-565.	0.7	3
529	Design of large-bandwidth single-mode operation waveguides in silicon three-dimensional photonic crystals using two guided modes. Optics Express, 2013, 21, 12443.	1.7	3
530	<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mi>p</mml:mi></mml:math>-shell carrier assisted dynamic nuclear spin polarization in single quantum dots at zero external magnetic field. Physical Review B, 2016, 93, .	1.1	3
531	Manipulation of dynamic nuclear spin polarization in single quantum dots by photonic environment engineering. Physical Review B, 2017, 95, .	1.1	3
532	Photoluminescence properties as a function of growth mechanism for GaSb/GaAs quantum dots grown on Ge substrates. Journal of Applied Physics, 2019, 126, .	1.1	3
533	Spin-dependent directional emission from a quantum dot ensemble embedded in an asymmetric waveguide. Optics Letters, 2019, 44, 3749.	1.7	3
534	Solution-Processed C60Single-Crystal Field-Effect Transistors. Japanese Journal of Applied Physics, 2012, 51, 11PD06.	0.8	3
535	The heat is on: towards the realization of non-cryogenic photonic quantum technologies. Materials for Quantum Technology, 2021, 1, 013001.	1.2	3
536	Long-term stability following surgical orthodontic treatment of mandibular prognathisms: investigation by means of lateral X-ray cephalogram. Bulletin of Tokyo Dental College, The, 1996, 37, 167-75.	0.1	3
537	Photoluminescence of GaAs-AlGaAs multiple quantum well structures under high excitation by a single shot of 30 ps, 532 nm laser. Surface Science, 1986, 174, 272-277.	0.8	2
538	Photoluminescence from point contact structure â€" Direct observation of electron flow. Physica B: Condensed Matter, 1996, 227, 77-81.	1.3	2
539	Influence of carrier transport/capture and gain flattening in picosecond pulse generation of InGaAs microcavity lasers. Applied Physics Letters, 1996, 69, 3137-3139.	1.5	2
540	Selective growth of GaAs quantum dots and vertical quantum wires in two-dimensional V-grooves. Physica E: Low-Dimensional Systems and Nanostructures, 1998, 2, 15-18.	1.3	2

#	Article	IF	Citations
541	Confined optical phonons in semiconductor quantum dots. Solid State Communications, 1999, 109, 351-356.	0.9	2
542	Spectroscopic discrimination of non-radiative centers in quantum wells by two wavelength excited photoluminescence. Journal of Crystal Growth, 2000, 210, 238-241.	0.7	2
543	Photoluminescence from two-dimensional electron gas in modulation-doped AlxGa1âˆ'xN/GaN heterostructures. Physica E: Low-Dimensional Systems and Nanostructures, 2000, 7, 939-943.	1.3	2
544	Effects of electronâ€"hole correlation in quantum dots under high magnetic field (up to 45 T). Physica E: Low-Dimensional Systems and Nanostructures, 2000, 7, 346-349.	1.3	2
545	Correlation Effects in Strain-Induced Quantum Dots. Physica Status Solidi (B): Basic Research, 2001, 224, 361-366.	0.7	2
546	Extremely Slow Relaxation Process of a Yellow-Luminescence-Related State in GaN Revealed by Two-Wavelength Excited Photoluminescence. Physica Status Solidi (B): Basic Research, 2001, 228, 433-436.	0.7	2
547	Observation of dip structures in PLE spectra of a highly excited single self-assembled quantum dot. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 13, 151-154.	1.3	2
548	Effect of strain variation on photoluminescence from InGaAs quantum dots in air-bridge structures. Physica Status Solidi (B): Basic Research, 2003, 238, 289-292.	0.7	2
549	Control of InxGa1-xAs Capping Layer Induced Optical Polarization in Edge-Emitting Photoluminescence of InAs Quantum Dots. Japanese Journal of Applied Physics, 2004, 43, 1978-1980.	0.8	2
550	Group Delay of a Coupled-Defect Waveguide in a Photonic Crystal. Optical Review, 2004, 11, 300-302.	1.2	2
551	Selective excitation of self-assembled quantum dots by using shaped pulse. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 21, 180-183.	1.3	2
552	Highly uniform self-assembled InAs/GaAs quantum dots emitting at 1.3Î¼m by metalorganic chemical vapor deposition. Physica E: Low-Dimensional Systems and Nanostructures, 2005, 26, 77-80.	1.3	2
553	Magneto-optical single dot spectroscopy of GaSb/GaAs type II quantum dots. Physica E: Low-Dimensional Systems and Nanostructures, 2006, 32, 152-154.	1.3	2
554	Esaki diodes live and learn. Proceedings of the Japan Academy Series B: Physical and Biological Sciences, 2010, 86, 451-453.	1.6	2
555	Magnetic field dependence of exciton fine structures in InAs/GaAs quantum dots: Exchange vs. Zeeman splittings. Physica E: Low-Dimensional Systems and Nanostructures, 2010, 42, 2532-2535.	1.3	2
556	Fabrication and characterization of a vertical pillar structure including a self-assembled quantum dot and a quantum well. Physica E: Low-Dimensional Systems and Nanostructures, 2010, 42, 2592-2594.	1.3	2
557	New method to isolate and distribute photoluminescence emissions from InAs quantum dots over a wide-wavelength range. Journal of Crystal Growth, 2011, 323, 250-253.	0.7	2
558	Effect of electronic structure on singleâ€photon emission in InAs/InP quantum dot with quasiâ€resonant excitation. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 417-419.	0.8	2

#	Article	IF	Citations
559	Structural and optical properties of m-plane GaN/AlGaN quantum wires grown by metalorganic chemical vapor deposition. Applied Physics Letters, 2011, 99, 113106.	1.5	2
560	Surface Modification of Polydimethylsiloxane Using Low Pressure Chemical Vapour Deposition of Poly-Chloro-p-Xylene. Journal of Nano Research, 2012, 20, 129-142.	0.8	2
561	A single-electron probe for buried optically active quantum dot. AIP Advances, 2012, 2, 032103.	0.6	2
562	Shape evolution of low density InAs quantum dots in the partial capping process by using As2 source. Journal of Crystal Growth, 2013, 378, 549-552.	0.7	2
563	Excess carrier lifetime in epitaxially grown layers of germanium on silicon. , 2015, , .		2
564	Optical Characteristics of a Multichannel Hybrid Integrated Light Source for Ultra-High-Bandwidth Optical Interconnections. Photonics, 2015, 2, 1131-1138.	0.9	2
565	Self-assembled formation of GaAsP nano-apertures above InAs/GaAs quantum dots by the thermal diffusion of phosphorus. Physica Status Solidi (B): Basic Research, 2016, 253, 659-663.	0.7	2
566	Excitation and emission dynamics of a single photon emitting InGaN quantum dot in a photonic horn structure. Superlattices and Microstructures, 2020, 145, 106575.	1.4	2
567	Optical Properties of Site-Controlled InGaAs Quantum Dots Embedded in GaAs Nanowires by Selective Metalorganic Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2012, 51, 11PE13.	0.8	2
568	Single photon generation from AlGaN exciton localization centers exhibiting narrow spectral linewidths. APL Materials, 2021, 9, 121106.	2.2	2
569	Use of high magnetic fields to estimate carrier leakage current in GaInAsPâ€InP double heterostructure lasers. Applied Physics Letters, 1984, 45, 7-9.	1.5	1
570	Wavelength switching of picosecond pulse (<10 ps) in a quantum well laser and its allâ€optical logic gating operations. Applied Physics Letters, 1991, 58, 1709-1711.	1.5	1
571	Near-field spectroscopy of single self-assembled InAs quantum dots: Observation of energy relaxation process. Microelectronic Engineering, 1999, 47, 111-113.	1.1	1
572	Excitonic resonant photorefractive devices around 1.06 Î¼m. Optical Materials, 2001, 18, 183-185.	1.7	1
573	Self-Assembled Growth of GaN Quantum Dots Using Low-Pressure MOCVD. Physica Status Solidi (B): Basic Research, 2001, 228, 191-194.	0.7	1
574	Dynamics and gain in highly-excited InGaN MQWs. Current Applied Physics, 2002, 2, 321-326.	1.1	1
575	Time-resolved gain dynamics in InGaN MQWs using a Kerr gate. Physica E: Low-Dimensional Systems and Nanostructures, 2003, 17, 255-257.	1.3	1
576	Subbands transport of the two-dimensional electron gas in AlxGa1â^'xN/GaN heterostructures. Optical Materials, 2003, 23, 139-141.	1.7	1

#	Article	IF	Citations
577	Long-lived excitons up to 1Î¼s in GaN/AlN self-assembled quantum dots. Physica Status Solidi (B): Basic Research, 2003, 240, 388-391.	0.7	1
578	Photo-induced absorption change for InGaN film by violet laser diode. Physica Status Solidi (B): Basic Research, 2004, 241, 2703-2707.	0.7	1
579	Time-integrated and time-resolved photoluminescence studies of InGaN quantum dots. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 568-572.	0.8	1
580	Sulfur-Terminated GaAs-Supported Pd Catalyst for the Heck Reaction. Synfacts, 2006, 2006, 1070-1070.	0.0	1
581	Processâ€free estimation of threshold current density of InAs quantum dot laser. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 2935-2937.	0.8	1
582	Formation of InAs1âˆ’xSbx quantum dots on vicinal InP(001) for 1.55-Î¼m DFB laser applications. Journal of Crystal Growth, 2008, 310, 2999-3003.	0.7	1
583	Design, fabrication and optical characterization of GaAs photonic crystal nanocavity lasers with InAs quantum dots gain wafer-bonded onto Si substrates. Physica E: Low-Dimensional Systems and Nanostructures, 2010, 42, 2560-2562.	1.3	1
584	Fabrication of high-Q silicon-based three-dimensional photonic crystal nanocavity and its lasing oscillation with InAs quantum-dot gain. , 2011, , .		1
585	Observation of Purcell effect in a 3D photonic crystal nanocavity with a single quantum dot. , 2011, , .		1
586	Rim formation on non-elongated InAs quantum dots grown by partial cap and annealing process at low temperature. Journal of Crystal Growth, 2013, 378, 558-561.	0.7	1
587	Design of highâ€‹<i>Q</i> nanocavity in threeâ€dimensional woodpile photonic crystal with vertically mirrorâ€symmetric structure. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 1457-1460.	0.8	1
588	(Invited) Si Waveguide-Integrated High-Speed Ge Photodetector. ECS Transactions, 2014, 64, 723-727.	0.3	1
589	InAs/GaAs quantum dot lasers metal-stripe-bonded onto SOI substrate. , 2014, , .		1
590	Optical anisotropy of m -plane nitride air-gap distributed Bragg reflector microcavities. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 840-843.	0.8	1
591	Direct modulation of InAs/GaAs quantum dot lasers on silicon at 60 Â°C. , 2016, , .		1
592	(Invited) Fabrication of Ge Waveguides by Epitaxial Lateral Overgrowth toward Monolithic Integration of Light Sources. ECS Transactions, 2016, 75, 199-209.	0.3	1
593	UV/Ozone-assisted bonding for InAs/GaAs quantum dot lasers on Si. , 2017, , .		1
594	A photonic crystal nanocavity with a quantum dot active region embedded by MBE regrowth. , 2017, , .		1

#	Article	IF	Citations
595	Observation of sharp emission lines from Zn-doped GaN. Japanese Journal of Applied Physics, 2019, 58, SCCB15.	0.8	1
596	The 1200â€‰nmâ€Band InAs/GaAs Quantum Dot Intermixing by Dry Etching and Ion Implantation. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 1900851.	0.8	1
597	Impact of Quantum Dots on III-Nitride Lasers: A Theoretical Calculation on Linewidth Enhancement Factors. IEEE Journal of Selected Topics in Quantum Electronics, 2022, 28, 1-7.	1.9	1
598	III-V/Si hybrid photonic devices by direct fusion bonding. , 0, .		1
599	Irinotecan and cisplatin therapy-induced neutropenia as a prognostic factor in patients with extensive-disease small cell lung cancer. Annals of Oncology, 2019, 30, ix27.	0.6	1
600	Modulation properties of semiconductor lasers.. The Review of Laser Engineering, 1987, 15, 250-257.	0.0	0
601	Field spectrum anisotropy in multiple quantum-well semiconductor lasers subjected to high magnetic fields. Superlattices and Microstructures, 1988, 4, 507-510.	1.4	0
602	Perspective of Semiconductor Lasers: Semiconductor Lasers with Nanostructures and Microcavity.. The Review of Laser Engineering, 1995, 23, 479-486.	0.0	0
603	Light emission from individual InAs/GaAs self-assembled quantum dots excited by tunneling current injection. Solid-State Electronics, 1998, 42, 1079-1082.	0.8	0
604	Introduction to the issue on nanostructures and quantum dots. IEEE Journal of Selected Topics in Quantum Electronics, 2000, 6, 405-407.	1.9	0
605	Introduction to the issue on nanostructures and quantum dots. IEEE Journal of Selected Topics in Quantum Electronics, 2002, 8, 969-971.	1.9	0
606	Saturation of gain in In0.02Ga0.98N/In0.16Ga0.84N MQW plasmas. Physica B: Condensed Matter, 2002, 314, 47-51.	1.3	0
607	Reflection Characteristics of Coupled-Defect-Type Photonic Crystals. Japanese Journal of Applied Physics, 2004, 43, 6104-6107.	0.8	0
608	Effects of InGaAs Insertion Layer on the Properties of High-Density InAs/AlAs Quantum Dots. Japanese Journal of Applied Physics, 2004, 43, 3828-3830.	0.8	0
609	Transition Energy Control via Strain in Single Quantum Dots Embedded in Micromachined Air-Bridge. Japanese Journal of Applied Physics, 2004, 43, 2069-2072.	0.8	0
610	Time-resolved gain saturation dynamics in InGaN multi-quantum well structures. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 2508-2511.	0.8	0
611	Quantum and transport scattering times in modulation-doped AlxGa1-xN/GaN single quantum wells. Applied Physics A: Materials Science and Processing, 2005, 80, 39-42.	1.1	0
612	Temperature-dependent conductance of quasi-one-dimensional electrons in a novel constricted channel with corrugated interfaces. Physica E: Low-Dimensional Systems and Nanostructures, 2006, 32, 337-340.	1.3	0

#	Article	IF	Citations
613	Electron transport and shell structures of single InAs quantum dots probed by nanogap electrodes. Physica E: Low-Dimensional Systems and Nanostructures, 2006, 32, 187-190.	1.3	0
614	Enhancement of Room Temperature Photoluminescence from InAs Quantum Dots by Irradiating Mn. Japanese Journal of Applied Physics, 2007, 46, L801-L803.	0.8	0
615	Demonstration of High-Q Photonic Crystal H1-defect Nanocavities after Closing of Photonic Bandgap. , 2007, , .		0
616	Resonant photoluminescence from crystalline Si with photonic crystal nanocavity structures. , 2007, , .		0
617	Photonic Crystal Nanocavity for Highly Efficient Lasers and Light Sources. Conference Proceedings - Lasers and Electro-Optics Society Annual Meeting-LEOS, 2007, , .	0.0	0
618	Prospects of Quantum Dots for Advanced Nanophotonic Devices. , 2007, , .		0
619	Evaluation of incorporation efficiency of group V source gases in metal organic chemical vapor deposition of GaInNAs for high quality 1.21Î¼m quantum-well ridge wave guide lasers. Journal of Crystal Growth, 2007, 298, 658-662.	0.7	0
620	Prerequisites of nanocavities for single artificial atom laser. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 2831-2834.	0.8	0
621	Preface: phys. stat. sol. (c) 5/9. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 2693-2696.	0.8	0
622	Observation of very narrow fine-structure splittings in self-assembled quantum dots by photocurrent spectroscopy. Physica E: Low-Dimensional Systems and Nanostructures, 2008, 40, 2192-2194.	1.3	0
623	Advances in quantum dots for semiconductor lasers and single photon emitters: From science to practical implementation. , 2008, , .		0
624	Advances in quantum dots and 2D/3D photonic crystal nanocavity based on micro-machining technology. , 2008, , .		0
625	Light-matter interaction in single quantum dot with photonic crystal nanocavity. , 2009, , .		0
626	Biexcitonic photocurrent induced by twoâ€photon process at a telecommunication band. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, 1445-1448.	0.8	0
627	Controlling the size of InAs quantum dots on Si1â^'xGex/Si(001) by metalorganic vapor-phase epitaxy. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2009, 165, 103-106.	1.7	0
628	Photonic crystal nanocavity lasers with InAs quantum dots bonded onto silicon substrates. , 2009, , .		0
629	Formation of Ge-diffusion-suppressed GaAs layers and InAs quantum dots on Ge/Si substrates. Journal of Crystal Growth, 2010, 312, 2919-2922.	0.7	0
630	Acoustic phonon effects on telecommunicationâ€band quantum dot exciton Rabi oscillation. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 2578-2581.	0.8	0

#	Article	IF	Citations
631	Proposal and design of III-V/Si hybrid lasers with current injection across conductive wafer-bonded heterointerfaces. , 2011, , .		0
632	Lasing Characteristics of a Quantum-Dot-3D-Photonic-Crystal-Nanocavity Coupled System: Interaction between Fully Confined Electrons and Photons. AIP Conference Proceedings, 2011, , .	0.3	0
633	III–V quantum dot lasers on Si substrates by wafer bonding. , 2012, , .		0
634	High-efficiency InAs/GaAs quantum dot solar cells by MOCVD. , 2012, , .		0
635	Advances in quantum dot lasers for telecom and silicon photonics applications. , 2012, , .		0
636	Single quantum dot-photonic crystal nanocavity laser. , 2012, , .		0
637	Self-frequency summing in photonic crystal nanocavity quantum dot lasers. , 2013, , .		0
638	Nonlinear photonics in single quantum dot-photonic crystal nanocavity couples systems. , 2013, , .		0
639	Suppression of multi-photon emission in 1.5-µm quantum-dot single-photon source. , 2013, , .		0
640	Large vacuum Rabi splitting in an H0 photonic crystal nanocavity-quantum dot system. , 2013, , .		0
641	Effect of SCH/barrier layer thickness on K-factor of quantum dot lasers. , 2013, , .		0
642	Athermal silicon optical interposers with quantum dot lasers operating from 25 to 125Â°C. Electronics Letters, 2014, 50, 1377-1378.	0.5	0
643	Influence of the relative positions of quantum dots and nanocavities on the optical coupling strength. , 2015, , .		0
644	Design of efficient photo-elastic modulator using quasi-1D phononic crystal cavity. , 2015, , .		0
645	1.3-μm Quantum-dot lasers integrated with spot-size converter for improved coupling efficiency to waveguide. , 2015, , .		0
646	P-117 Phase II study of combination chemotherapy of gemcitabine/S-1 with nafamostat mesilate for advanced unresectable pancreatic cancer. First report. Annals of Oncology, 2016, 27, ii34.	0.6	0
647	Progress in quantum dots for advanced photonics. , 2017, , .		0
648	Imaging of topologically protected elastic mode in silica 1D phononic crystal via photoelastic effect. , 2017, , .		0

#	Article	IF	Citations
649	Eâ€band InAs/GaAs Triâ€layer Quantum Dot Lasers. Physica Status Solidi (A) Applications and Materials Science, 0, , 2100419.	0.8	0
650	Resonant-Wavelength Control in Visible-Light Range of Organic Photonic Crystal Nanocavities. Japanese Journal of Applied Physics, 2006, 45, 6112-6115.	0.8	0
651	Cavity Quantum Electrodynamics in Semiconductors: Quantum Dot-Photonic Crystal Nanocavity Coupled Systems. The Review of Laser Engineering, 2013, 41, 485.	0.0	0
652	Ultrafast quantum well optical devices.. The Review of Laser Engineering, 1987, 15, 1011-1015.	0.0	0
653	Epitaxial Growth Controlled in Three Dimensions. Self-Assembling of Quantum Boxes using Stranski-Krastanov Growth Mode.. Hyomen Kagaku, 1995, 16, 624-630.	0.0	0
654	Semiconductor Nanotechonogies and Optical Devices of Next Generarion. The Review of Laser Engineering, 1996, 24, 246-250.	0.0	0
655	Prospect of Nanostructure Optical Devices.. The Review of Laser Engineering, 1998, 26, 615-619.	0.0	0
656	Special Issue on Prospects of Photonic Functional Devices. The Review of Laser Engineering, 1998, 26, 588-588.	0.0	0
657	Advances in Quantum Dot Lasers for High Efficiency and High Output Power Operation. The Review of Laser Engineering, 2019, 47, 210.	0.0	0
658	Topological Photonic Crystal Nanocavities. The Review of Laser Engineering, 2019, 47, 351.	0.0	0
659	Local tuning of transfer-printed quantum-dot single-photon sources on a CMOS silicon chip. , 2019, , .		0
660	High-Density Silicon Photonics Integrated Technology for Photonics-Electronics Convergence System. The Review of Laser Engineering, 2020, 42, 217.	0.0	0
661	Hybrid integrated light sources on silicon assembled by transfer printing. , 2021, , .		0
662	InAs/InGaAs Quantum Dot Lasers on Multi-Functional Metamorphic Buffer Layers : Erratum. Optics Express, 2022, 30, 6617.	1.7	0
663	Quantum-chemical and physico-chemical properties of hydrochlorothiazide. Arzneimittelforschung, 1983, 33, 688-91.	0.5	0